

Grafen



Nobelova cena za fyziku 2010

Ludvík Smrčka

Fyzikální ústav AVČR v. v. i.

Praha

25.10.2012

Andre Geim



Flying frog



The Nobel Prize in Physics 2010 was awarded jointly
to Andre Geim and Konstantin Novoselov

"for groundbreaking experiments
regarding the two-dimensional
material graphene"

Nobelova cena za fyziku 2010



Andre Geim

Konstantin Novoselov

Za co byla cena udělena:

Andre Geim a Konstantin Novoselov

“za průlomové experimenty týkající
se dvojrozměrného uhlíkového
krystalu – grafenu”

Trocha historie.....

- 1946 transistor
- 2000 Nanotechnologická iniciativa (Bill Clinton)
- Jak nahradit křemík?

Motivace...

- Najít alternativu k současným křemíkovým MOSFETům a GaAs/AlGaAs HEMTům
- Aby nebylo moc volných elektronů je třeba tenká vrstva ...
- Neměla by být kovová...
- Nejvhodnějším kandidátem je grafit

Polovodiče (Si, Ge, A^{III}B^V, A^{II}B^{VI})

1 H 1.0079																	2 He		
3 Li 6.941	4 Be 9.0122																		
11 Na 22.990	12 Mg 24.305																		
19 K 39.098	20 Ca 40.078	21 Sc 44.956	22 Ti 47.867	23 V 50.942	24 Cr 51.996	25 Mn 54.938	26 Fe 55.845												
37 Rb 85.468	38 Sr 87.62	39 Y 88.906	40 Zr 91.224	41 Nb 92.906	42 Mo 95.94	43 Tc (98)	44 Ru 101.07												
55 Cs 132.91	56 Ba 137.33	57 - 71 *	72 Hf 178.49	73 Ta 180.95	74 W 183.84	75 Re 186.21	76 Os 190.23												
87 Fr (223)	88 Ra (226)	89 - 103 **	104 Rf (261)	105 Db (262)	106 Sg (263)	107 Bh (264)	108 Hs (265)												
* Lanthanide series		57 La 138.91	58 Ce 140.12	59 Pr 140.91	60 Nd 144.24	61 Pm (145)	62 Sm 150.36												
** Actinide series		89 Ac (227)	90 Th 232.04	91 Pa (231)	92 U 238.03	93 Np (237)	94 Pu (244)	(243)	(247)	(247)	(251)	(252)	(257)	(258)	(259)	(262)			

5 B 10.811	6 C 12.011	7 N 14.007	8 O 15.999
13 Al 26.982	14 Si 28.086	15 P 30.974	16 S 32.066
30 Zn 65.39	31 Ga 69.723	32 Ge 72.61	33 As 74.922
48 Cd 112.41	49 In 114.82	50 Sn 118.71	51 Sb 121.76
			52 Te 127.60

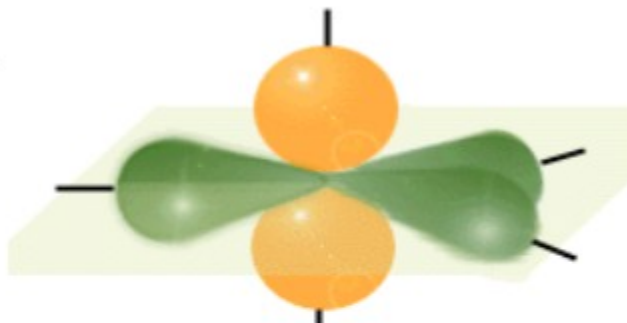
■ Radioactive element (all isotopes are unstable)

Numbers in parenthese are mass numbers of most stable nuclide of that element

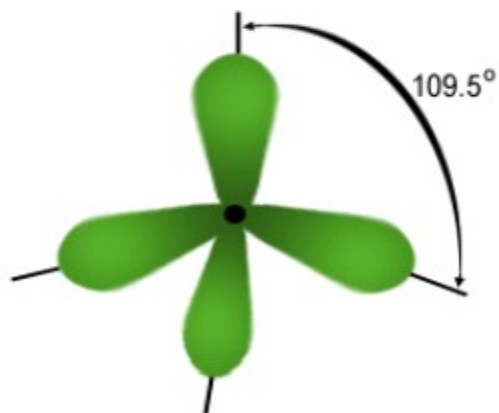
Čtyři valenční elektrony v buňce

Orbitály atomu uhlíku

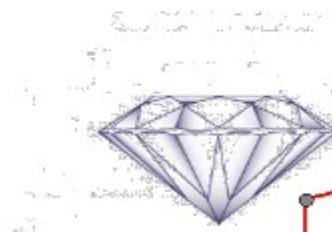
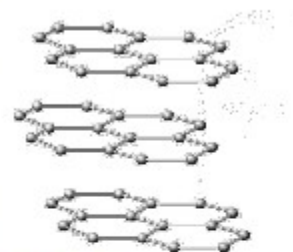
sp^2



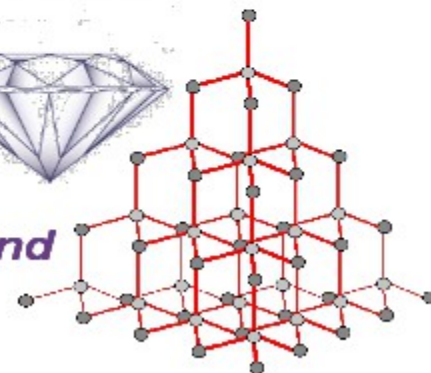
sp^3



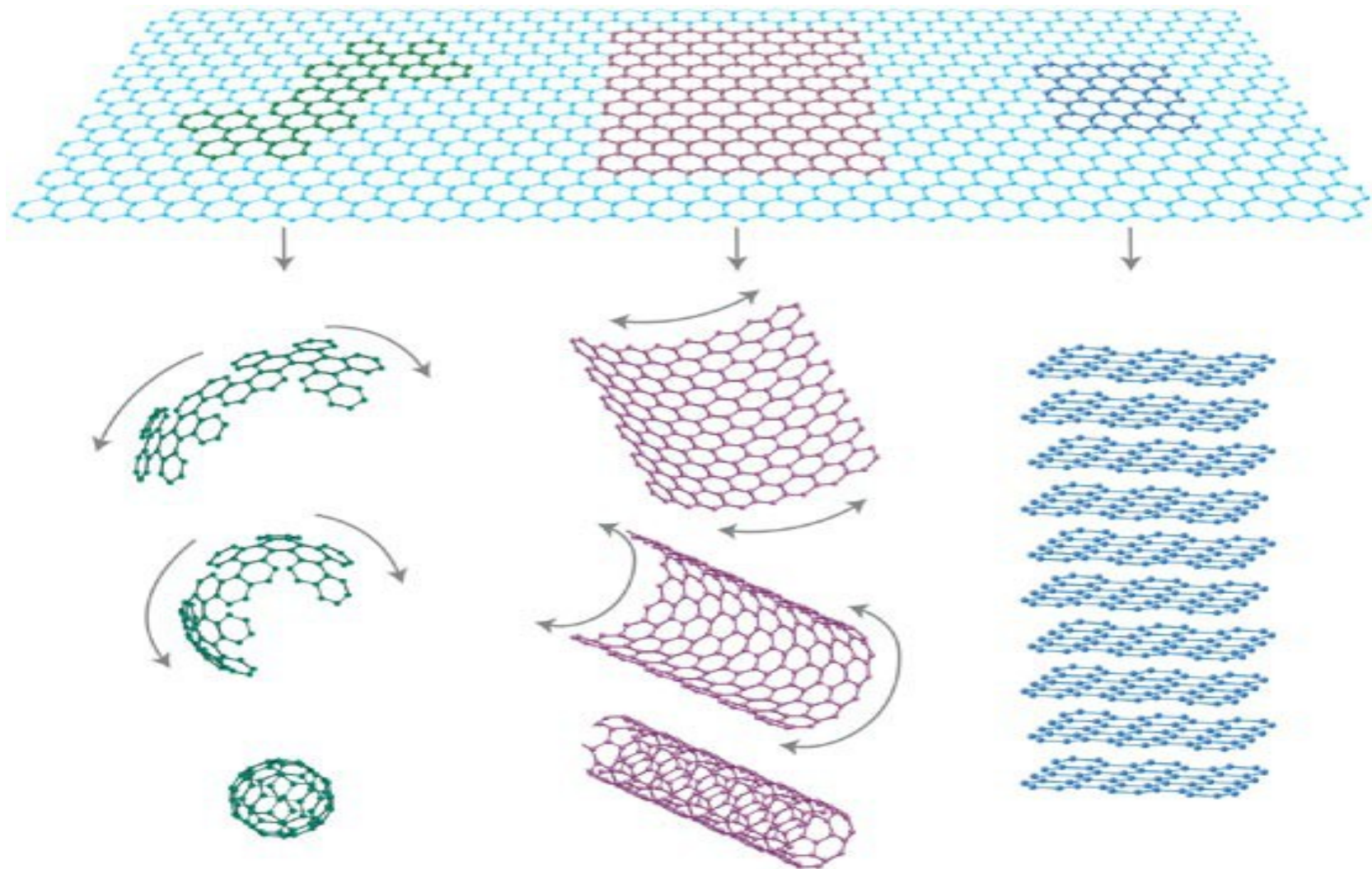
Graphite



Diamond



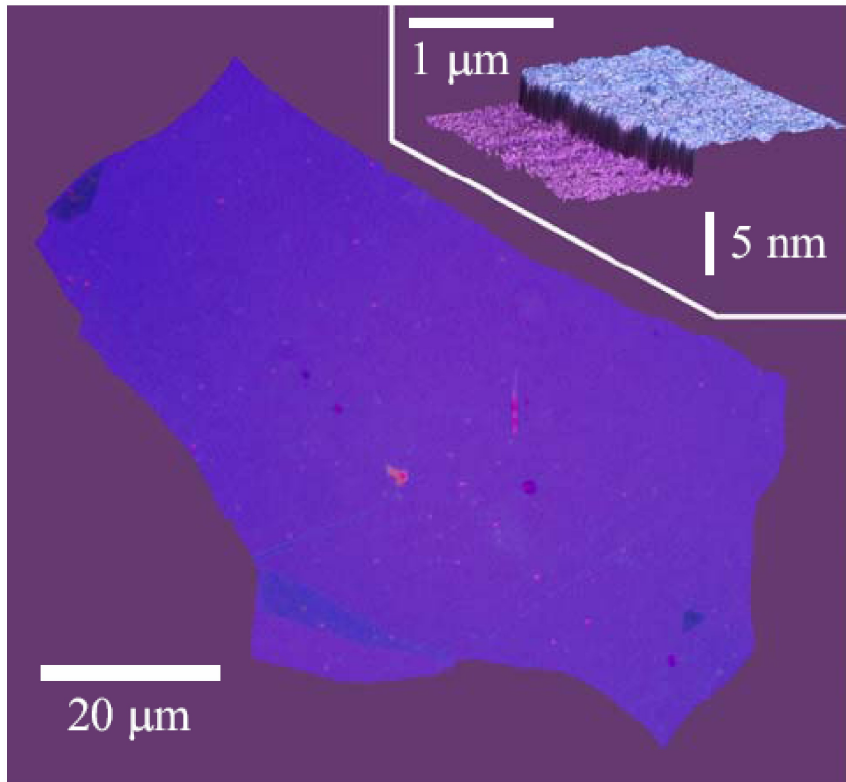
Grafen – matka všech struktur jak připravit?



Příprava grafitových vrstev exfoliací

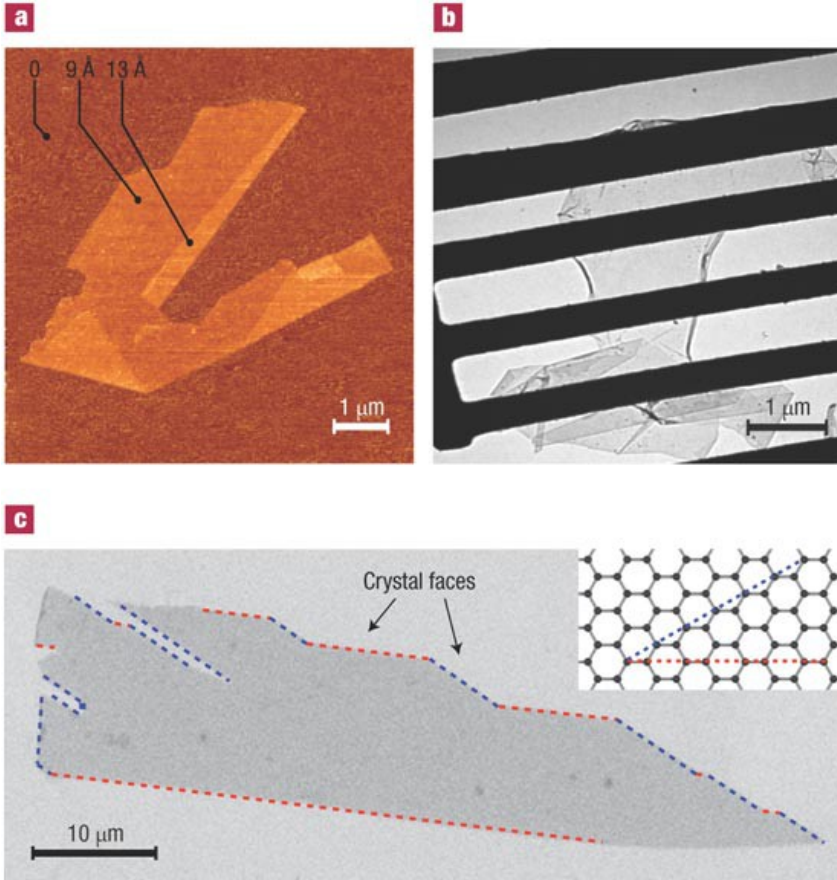
- Exfoliace – sejmutí vrstvy lepicí páskou
- Deposice vrstev na 300 nm SiO na povrchu křemíku (100)
- Identifikace vloček optickým a AFM mikroskopem

Několik vrstev grafenu



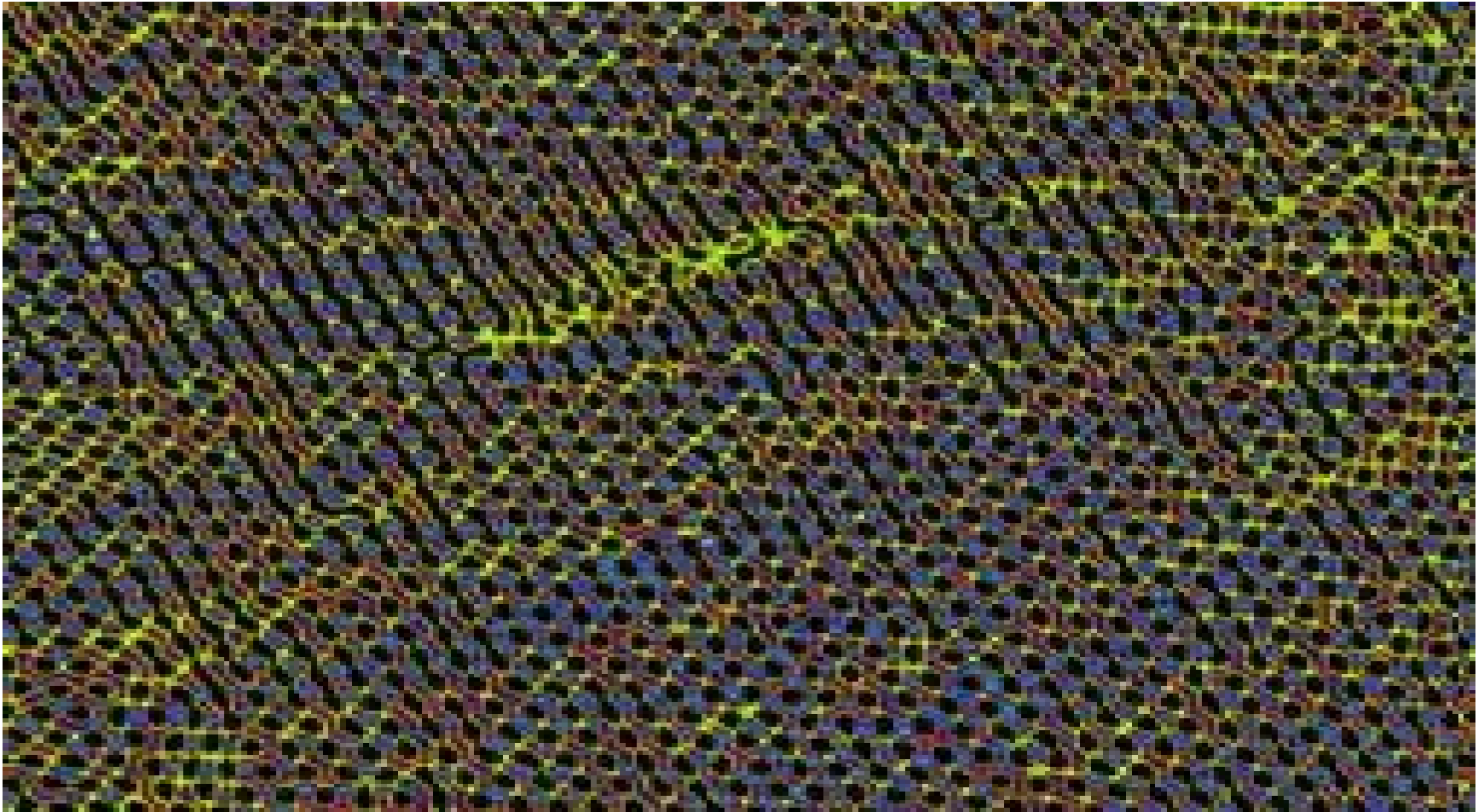
- Obrázek grafitového filmu z optického mikroskopu
- Vložen je obrázek z AFM mikroskopu
- Vzorek připravený izolepou

Jedna grafenová vrstva

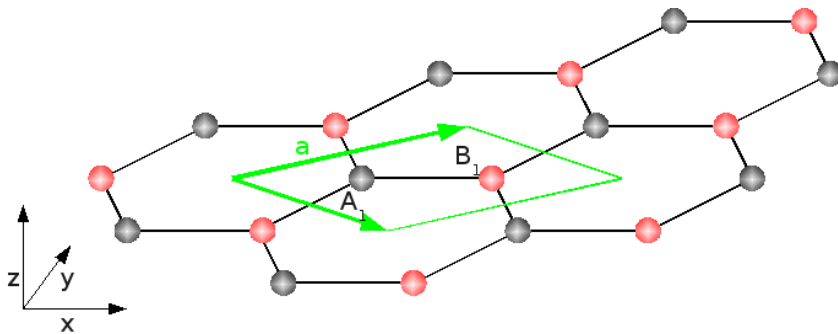


- „Psaní tužkou“
(Micromechanical cleavage)
- identifikace optickým mikroskopem
- potvrzeno AFM

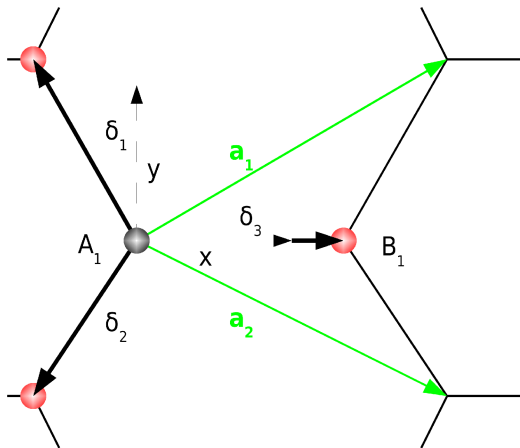
Grafen skanujícím transmisním mikroskopem



Graphene – krystalová struktura



- graphite – Bernal stacking of weakly coupled single sheets
-----**graphenes**-----
- two** atoms in a cell of a hexagonal Bravais lattice
- nearest neighbors tight binding electronic bands



Elektronová struktura grafenu

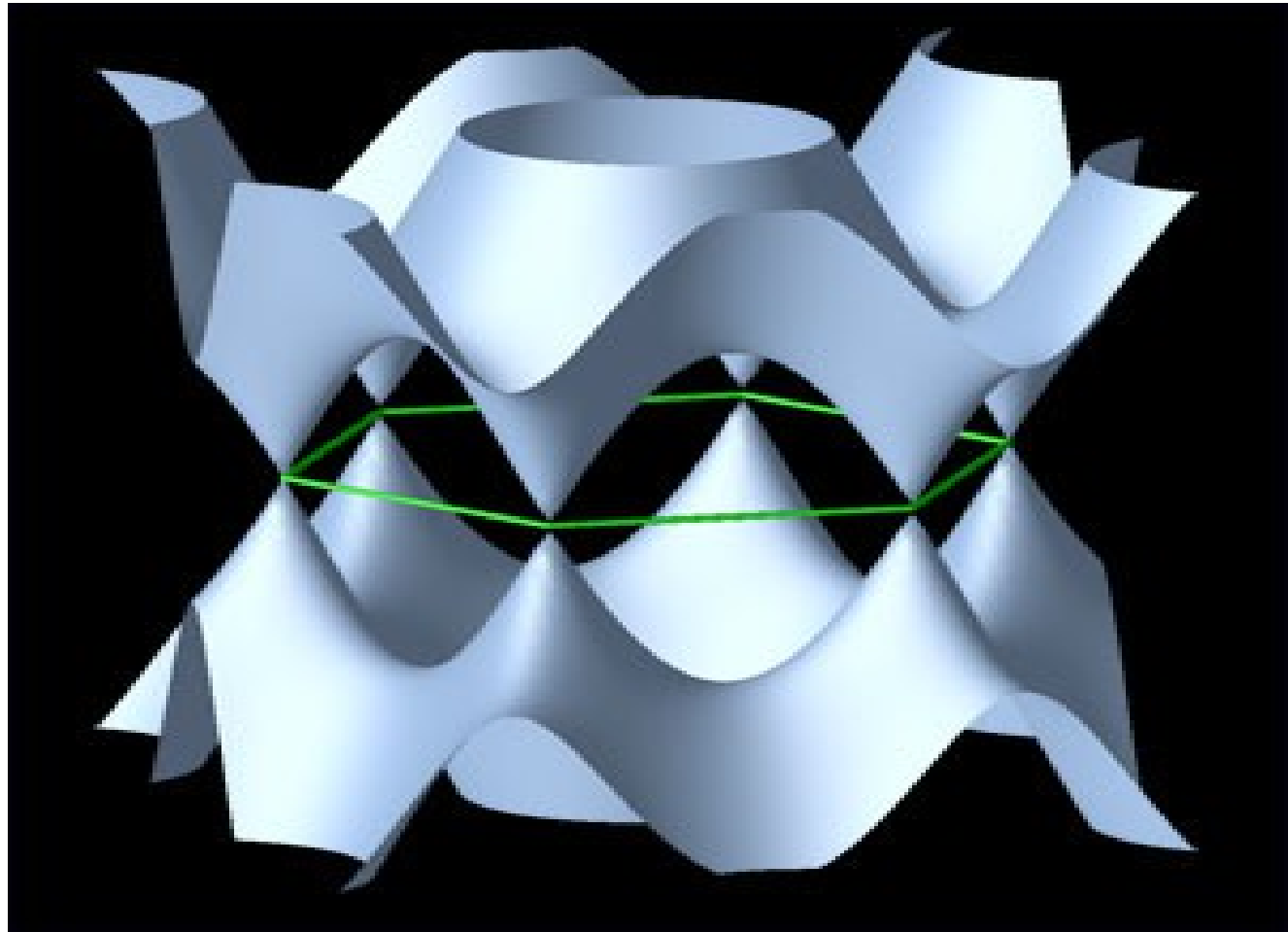
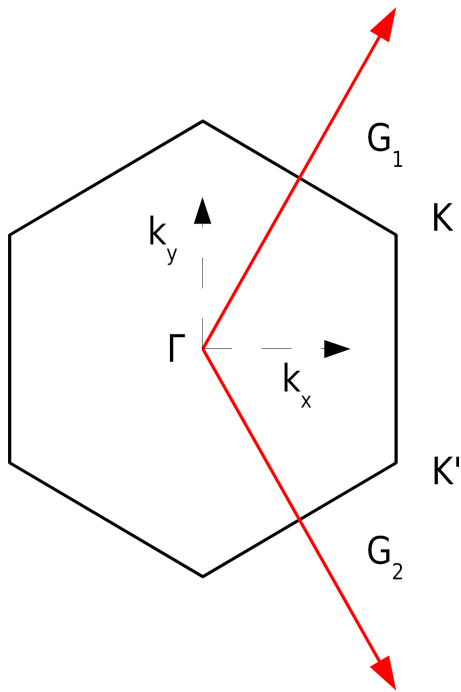
$$\Psi = a\Phi_{A1} + b\Phi_{B1}$$

$$\Phi_{A1} = \sum_{A1} \exp(i\vec{k} \cdot \vec{R}_{A1}) \chi(\vec{r} - \vec{R}_{A1}) \quad \Phi_{B1} = \sum_{B1} \exp(i\vec{k} \cdot \vec{R}_{B1}) \chi(\vec{r} - \vec{R}_{B1})$$

$$\begin{vmatrix} H_{A1A1} - E & H_{A1B1} \\ H_{B1A1} & H_{B1B1} - E \end{vmatrix} = 0$$

$$E_{\pm}(k_x, k_y) = \pm \sqrt{1 + 4\cos^2\left(\frac{k_y a}{2}\right) + 4\cos\left(\frac{k_x \sqrt{3} a}{2}\right)\cos\left(\frac{k_y a}{2}\right)}$$

Elektronová struktura grafenu



Dirac massless fermions

- Power series expansion around K and K', conical low-energy spectrum, Dirac point

$$E(\vec{k}) = \pm \hbar v_F k$$

$$E^2 = \cancel{m_0^2} + c^2 p^2$$

massless

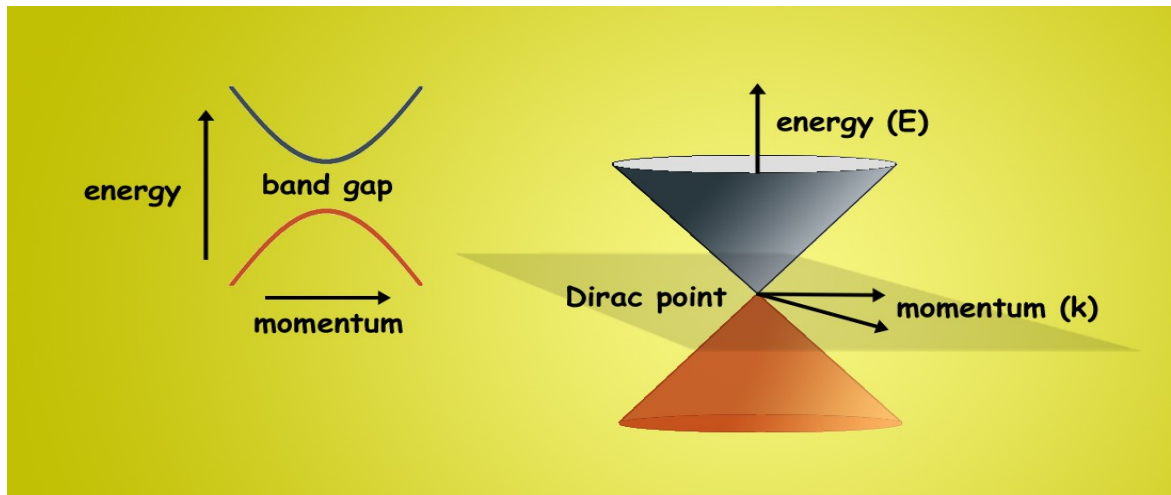
Schrödinger and Dirac fermions

$B=0$

$$E^S(\vec{k}) = \frac{\hbar^2 k^2}{2\tilde{m}}$$
$$\frac{1}{\tilde{m}} = \frac{1}{\hbar^2} \frac{\partial^2 E(\vec{k})}{\partial k^2}$$

$$E^D(\vec{k}) = \pm \hbar v_F k$$

$$\vec{v} = \frac{1}{\hbar} \nabla_{\vec{k}} E(\vec{k})$$



Transportní vlastnosti v magnetickém poli a kvantový Hallův jev

Klaus von Klitzing

🏆 1985



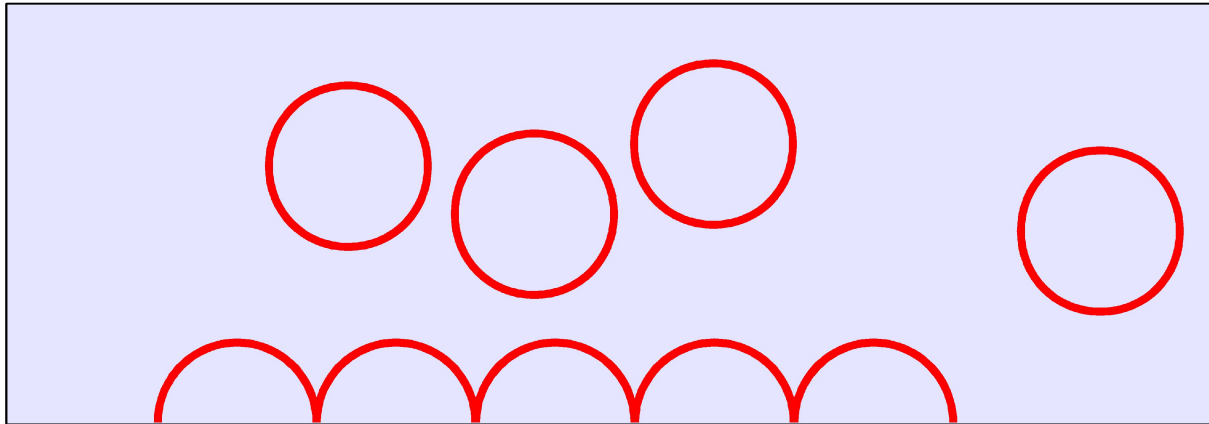
Horst Stormer

🏆 1998



2DEG v magnetickém poli

Lorentzova rovnice cyklotronový pohyb a hranové orbity

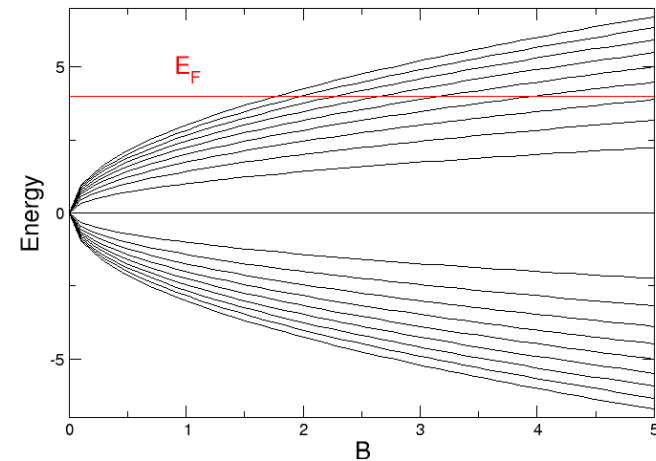
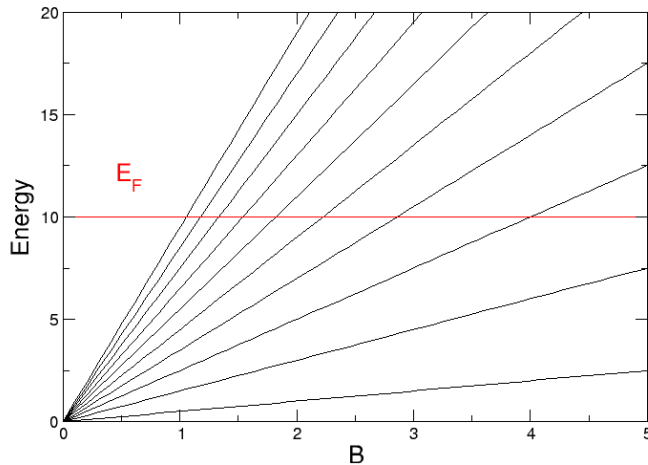


Schrödinger and Dirac fermions

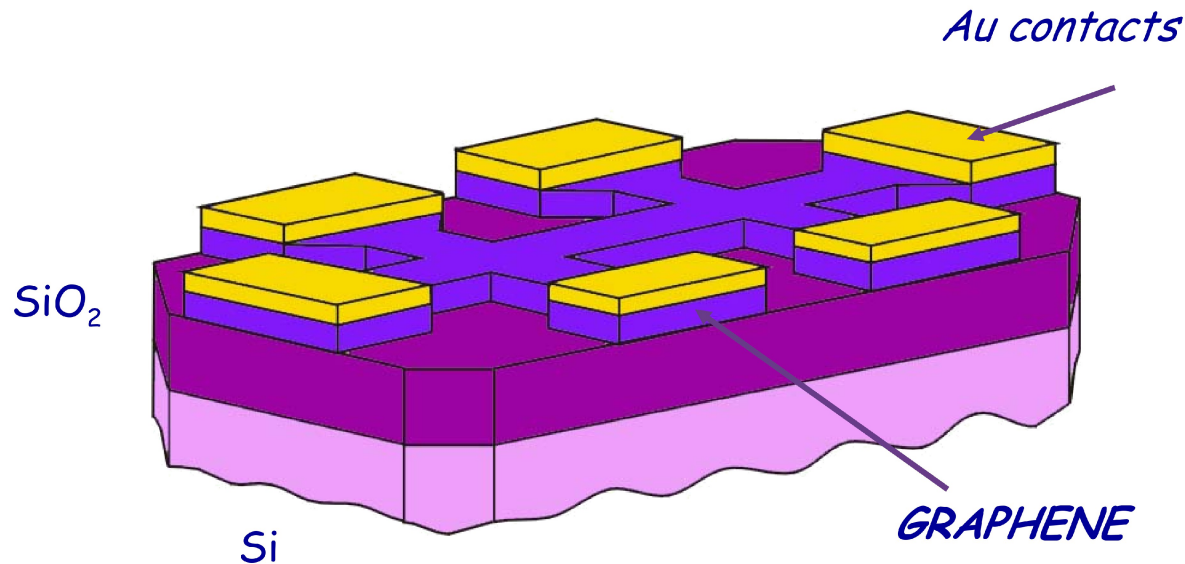
$B \neq 0$ Landau levels

$$E_n^S = \hbar \omega_c \left(n + \frac{1}{2} \right)$$
$$\omega_c = |e| B / m$$

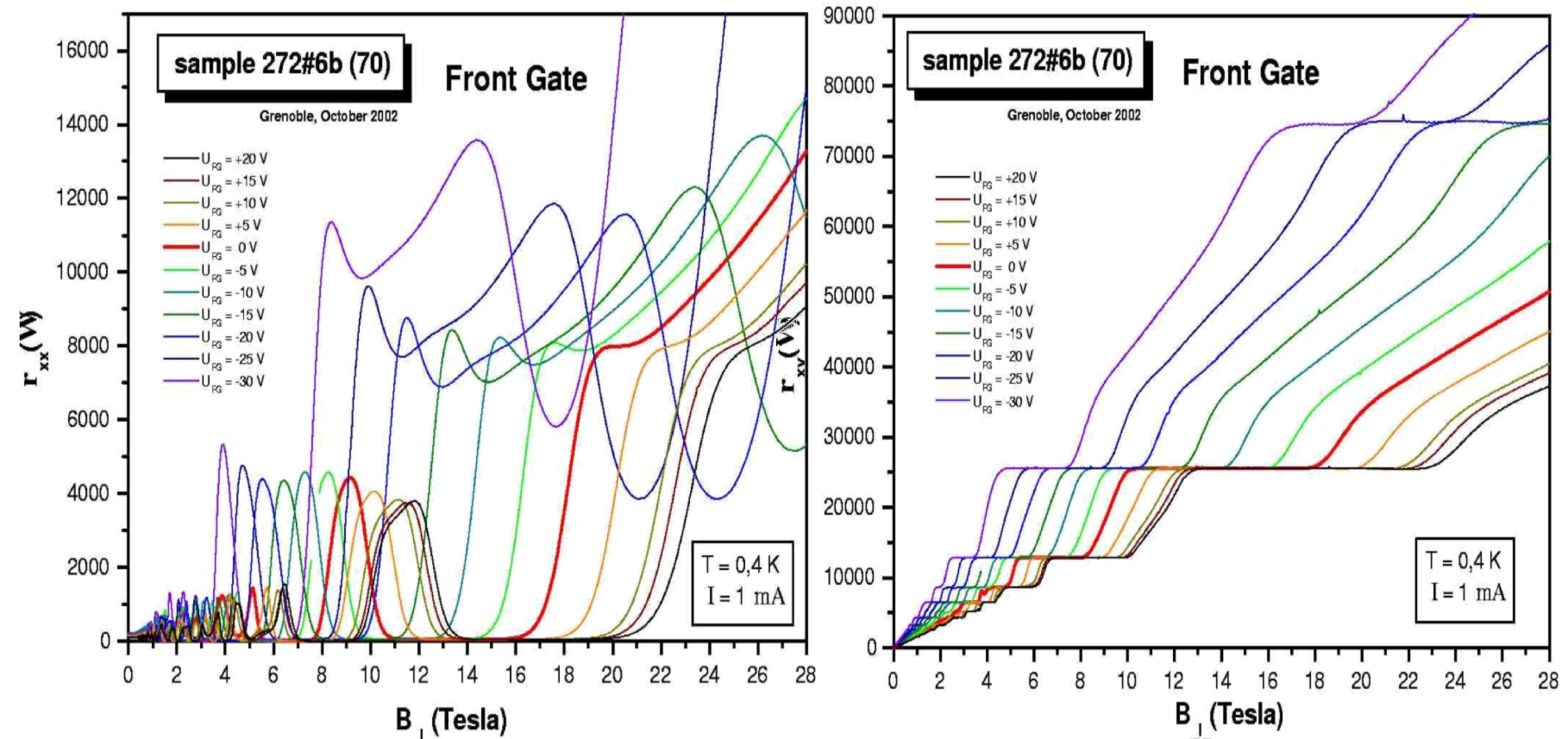
$$E_n^D = \pm \sqrt{2 \hbar |e| v_F^2 B n}$$
$$n = 0, 1, 2, \dots$$



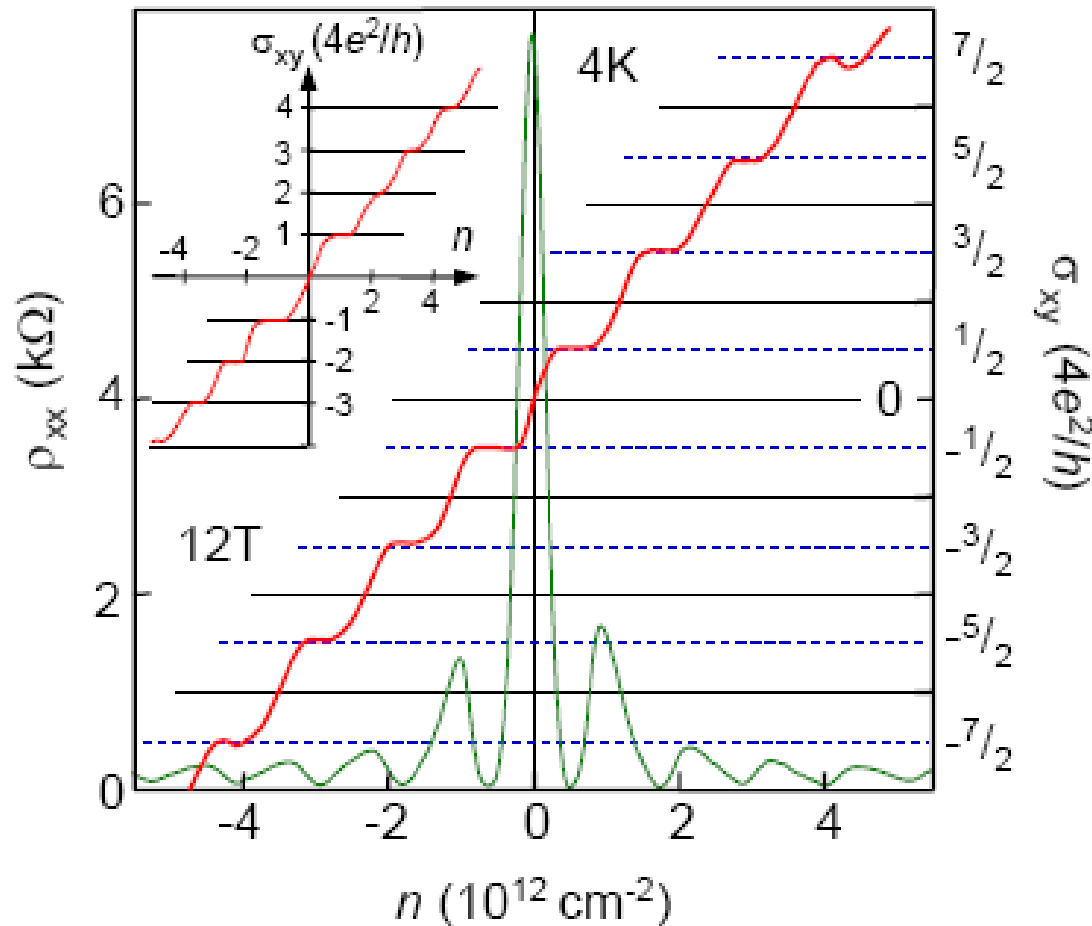
Schema vzorku pro transportní měření (elektronová litografie)



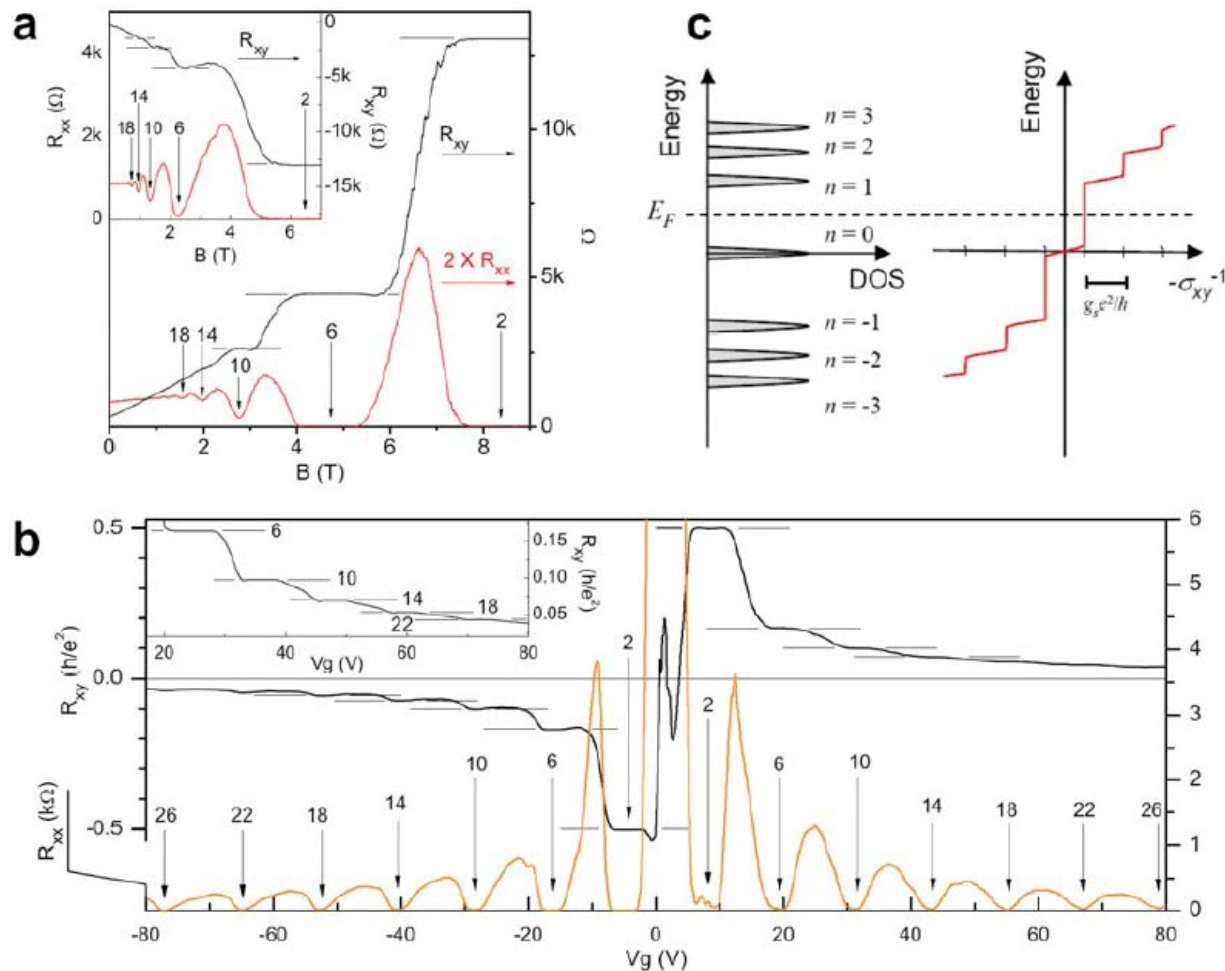
Hallův jev Schrodingerových elektronů



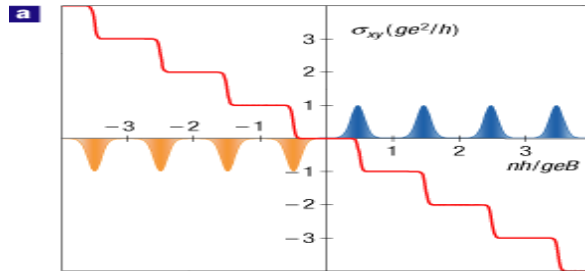
Poločíselný QHE v grafenu v závislosti na napětí



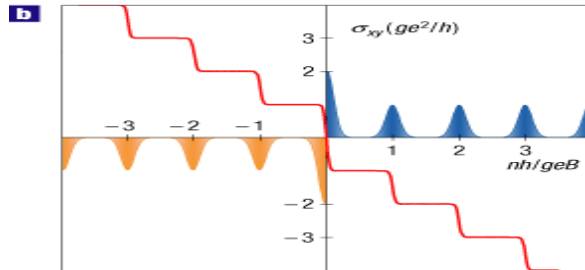
Měření na nejlepších vzorcích, závislost na magnetickém poli



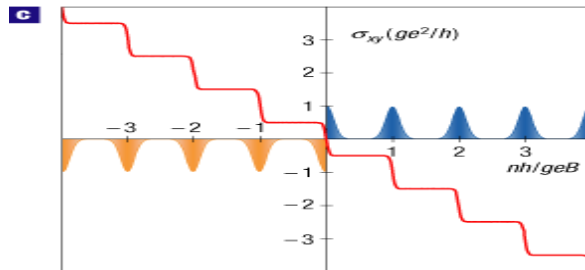
QHE v závislosti na napětí



a) Standardní
2DEG

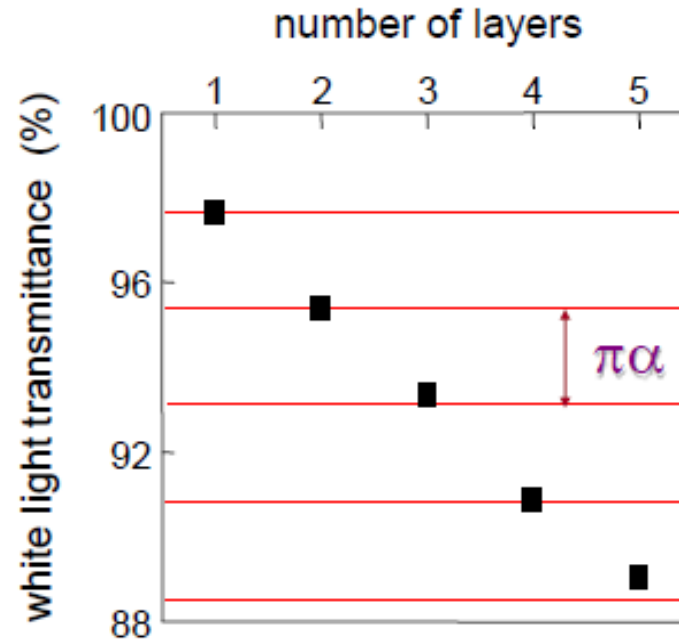
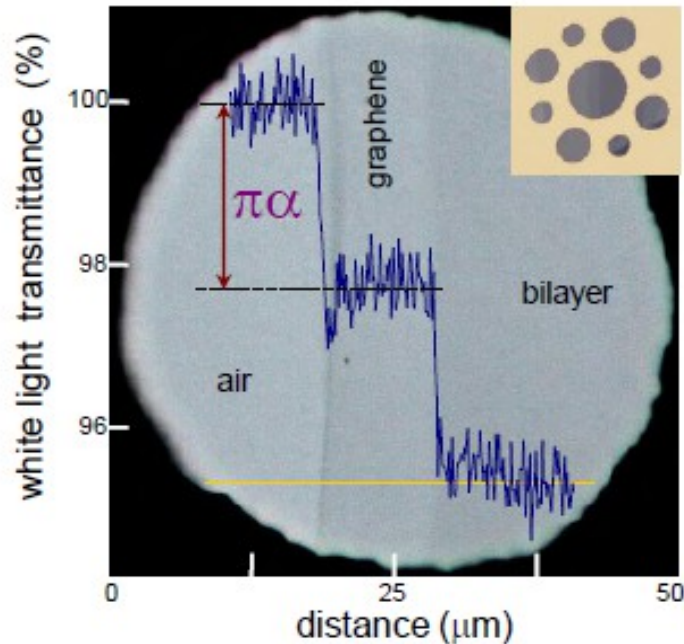


a) Bilayer graphene



a) Single layer
graphene

Visualisation of fine structure constant



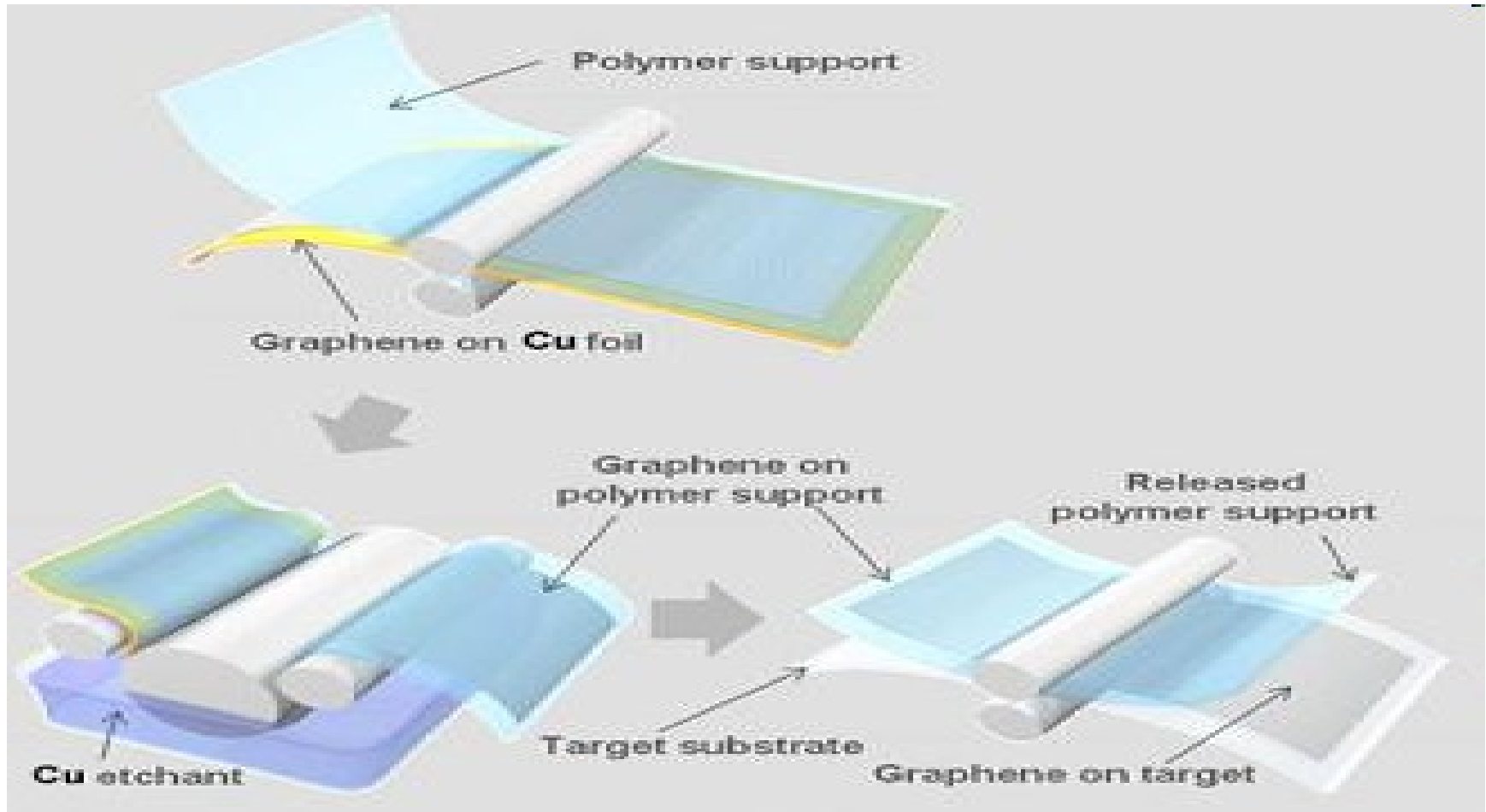
The fine structure constant observed “with a naked eye”

$$\alpha = 1/137 (\pm 2\%)$$

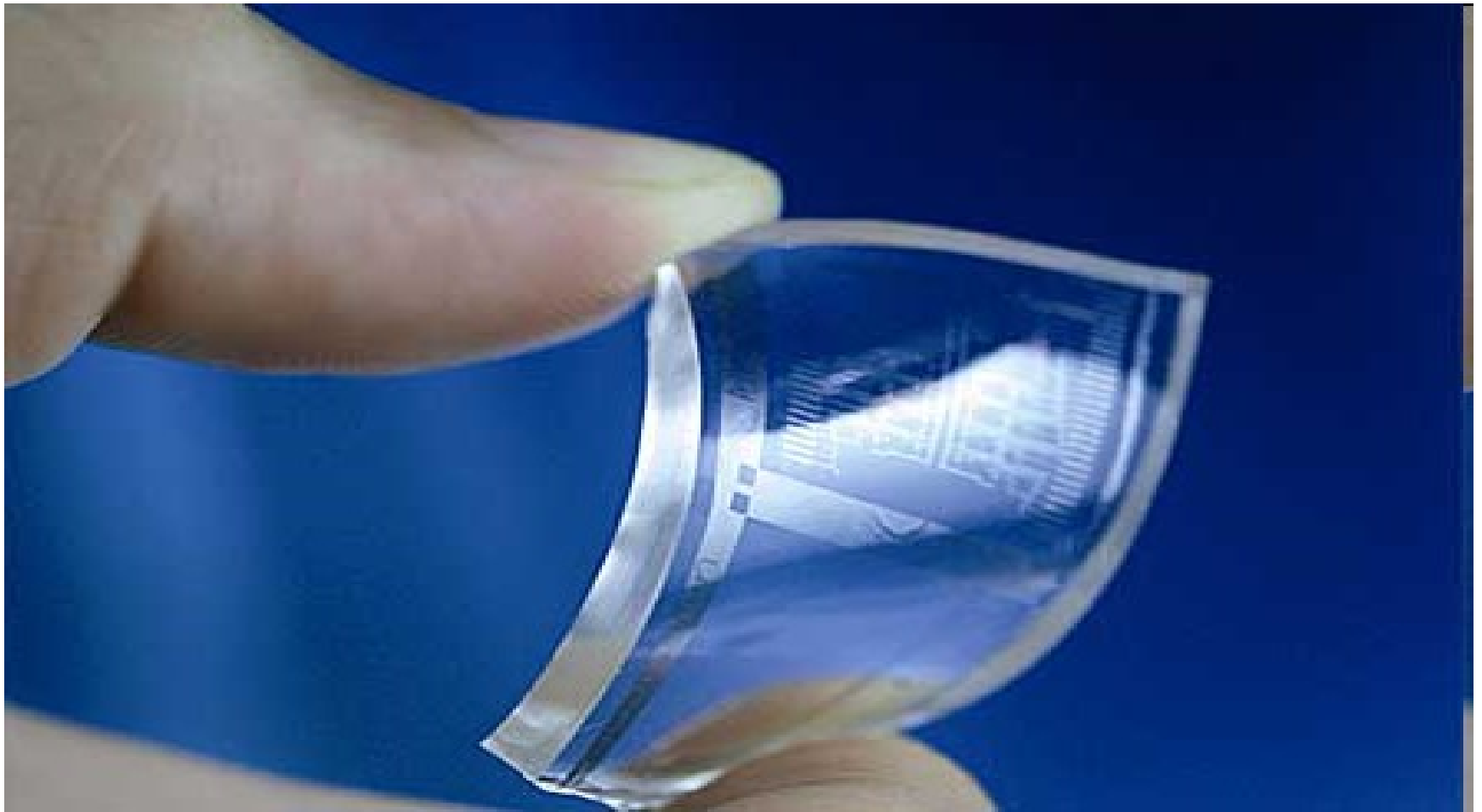
Příprava grafenu

Příprava grafenu depozicí na kov

M. Kalbáč UFCH JH



Folie s grafenem



Příprava grafenu na povrchu SiC

Epitaxial GrapheneLab - Georgia Institute of Technology



Nobel Laureate Albert Fert (center) is working with physicists Claire Berger and Walt de Heer (left to right)

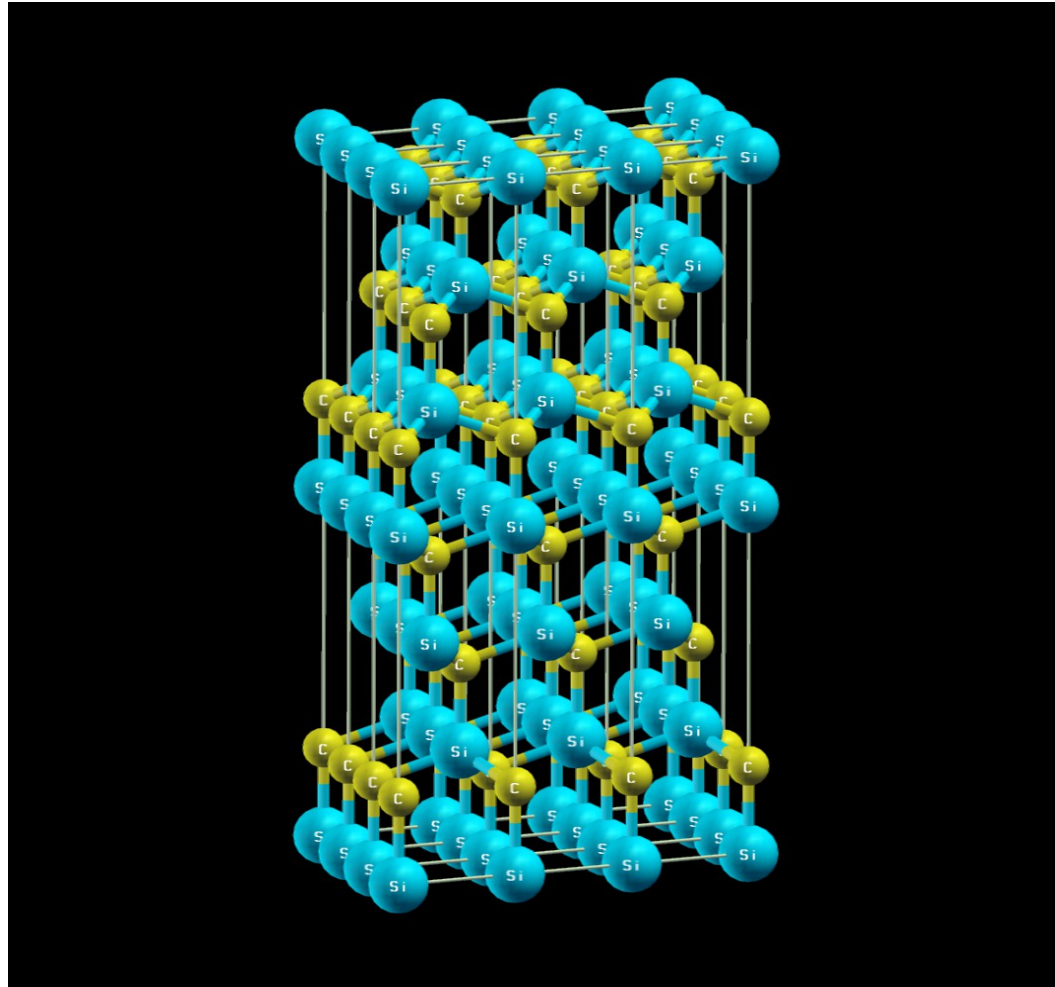


Epitaxial Graphene Transistor (EPIGRAT)

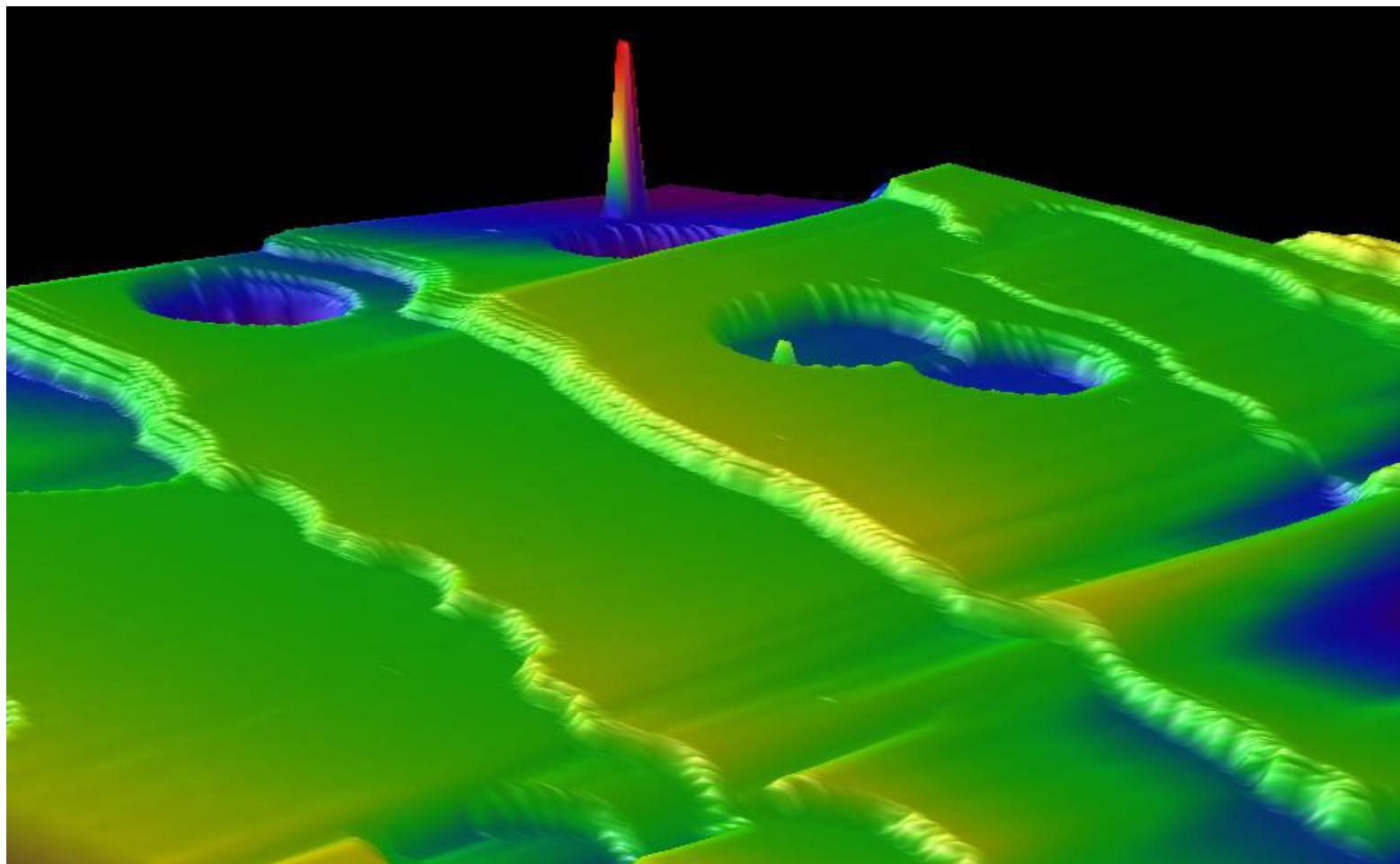
The aim of EPIGRAT is to synthesize and characterize epitaxial graphene layers on silicon carbide suitable for future electronics using different growth techniques, and to develop and characterize high frequency transistors made from these materials.

Švédsko, Polsko, Turecko, Francie a Česká republika

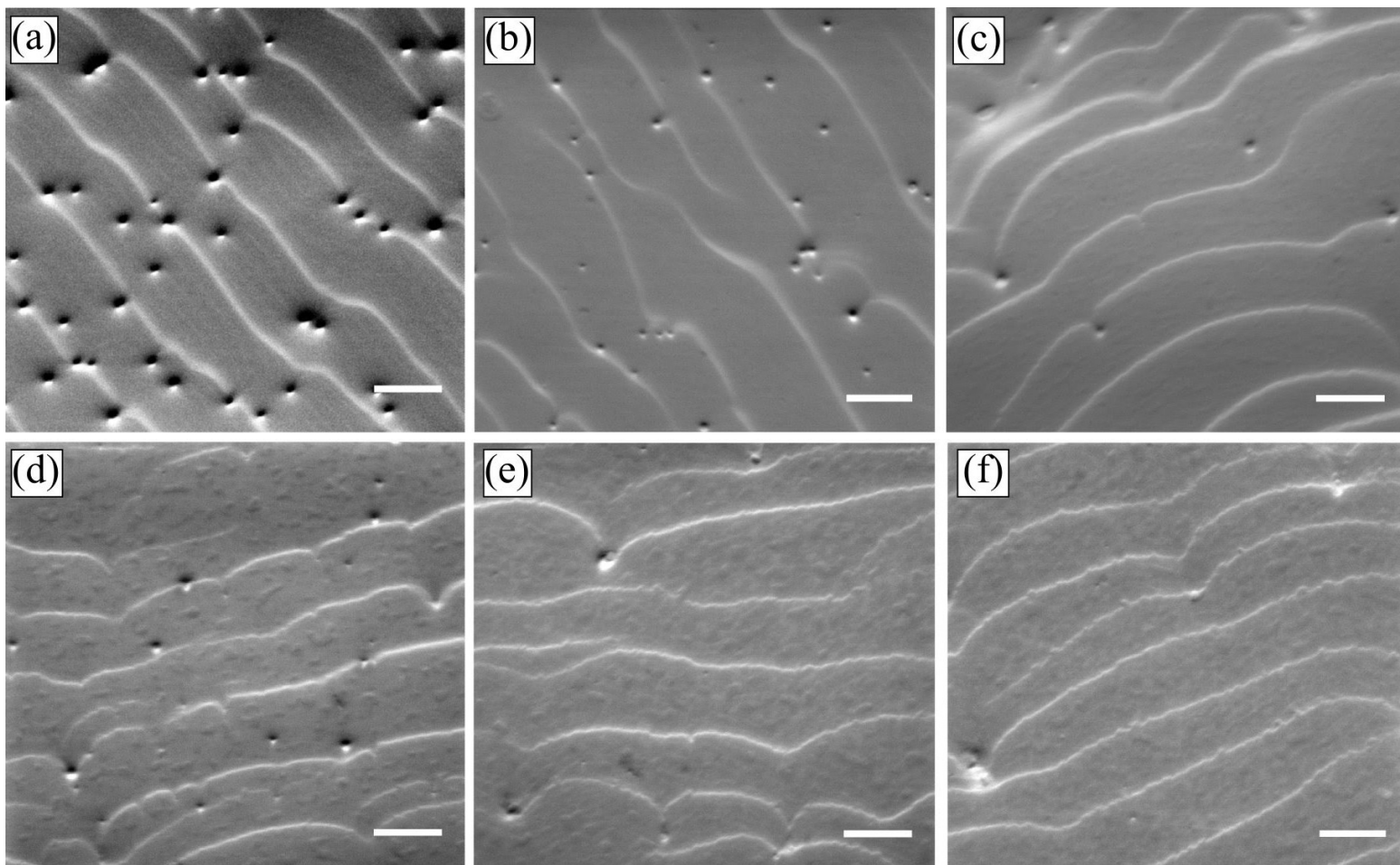
SiC crystal structure



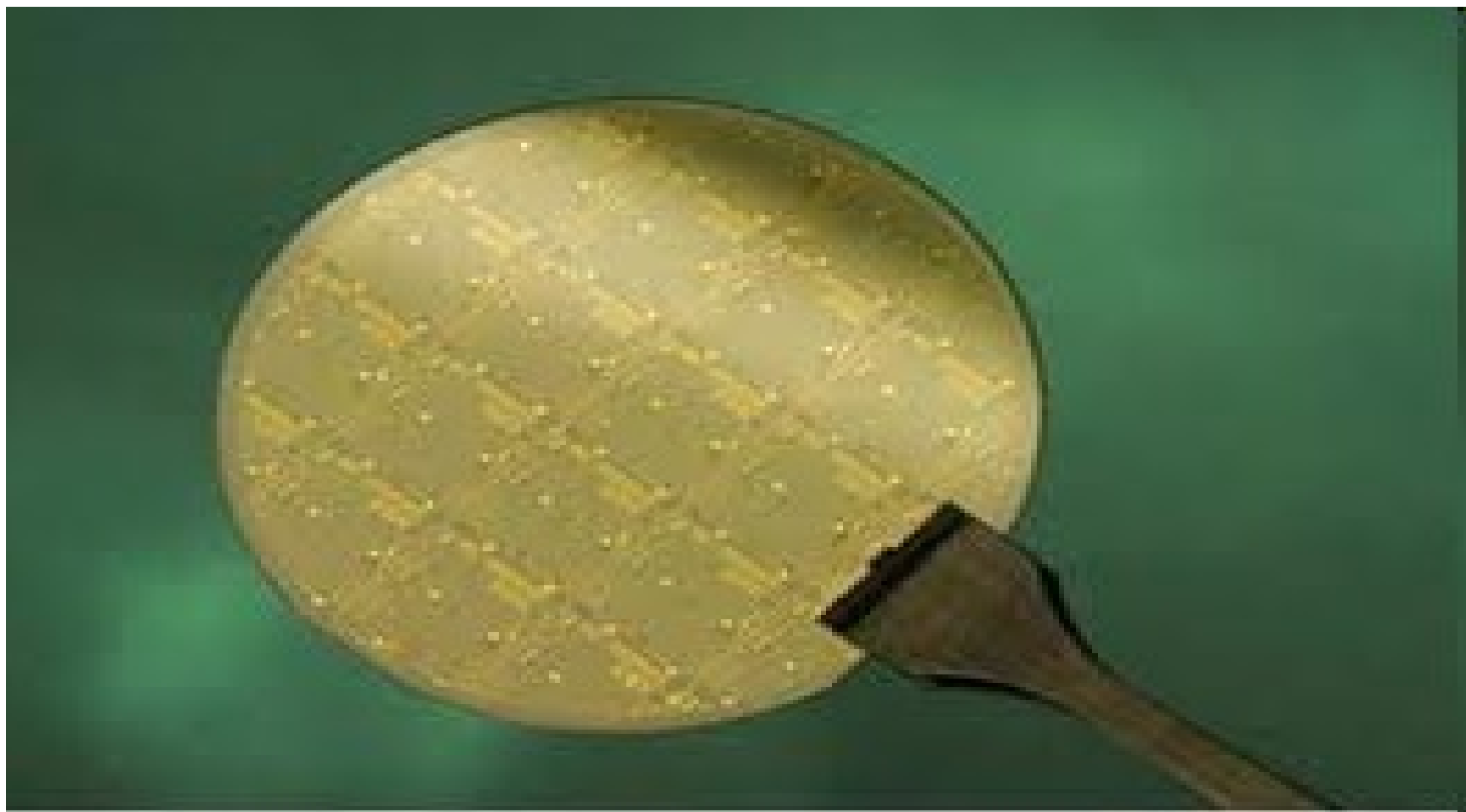
Povrch SiC



Příprava grafenu na karbidu křemíku

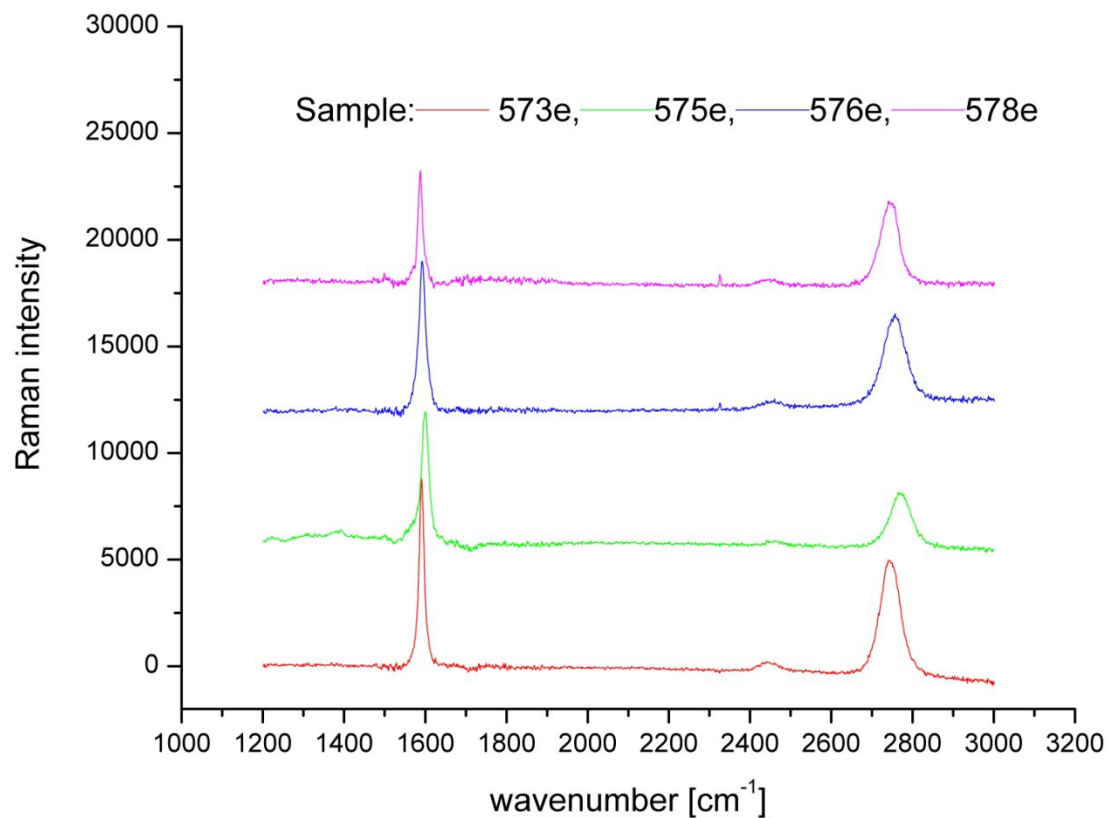


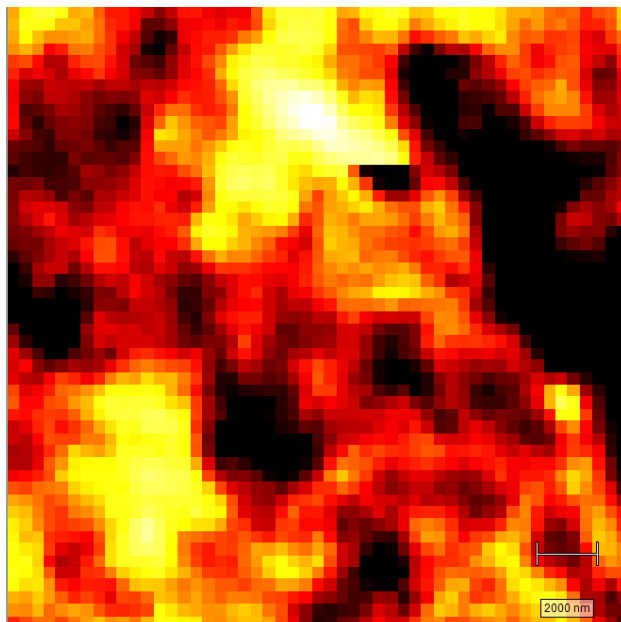
Grafen na podložce SiC



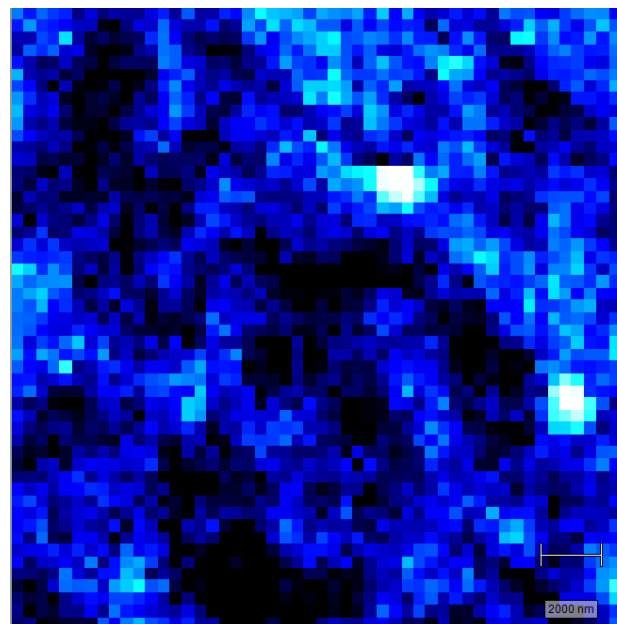
Ramanova spektra grafenu na SiC

M. Ledinský FZU



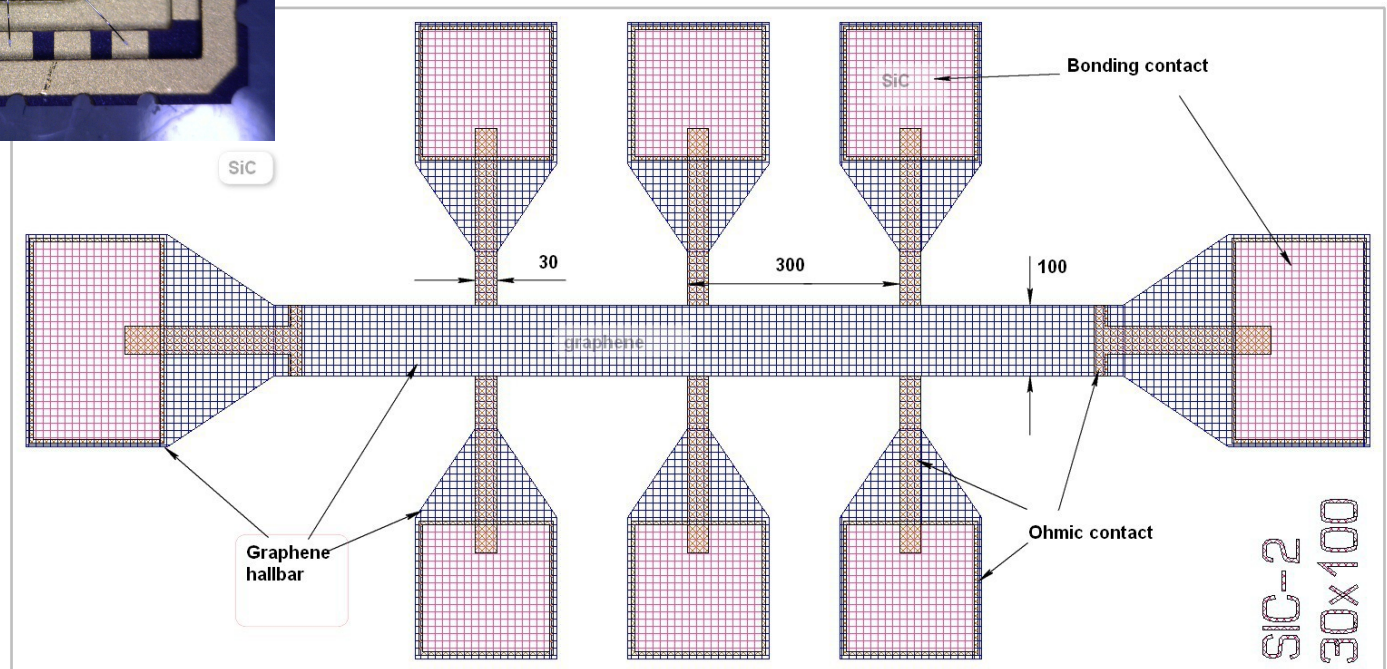
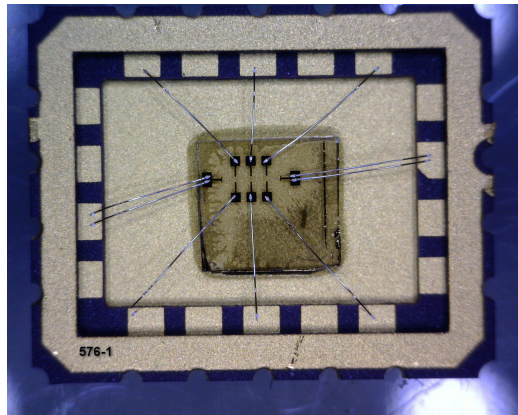


lokální napětí



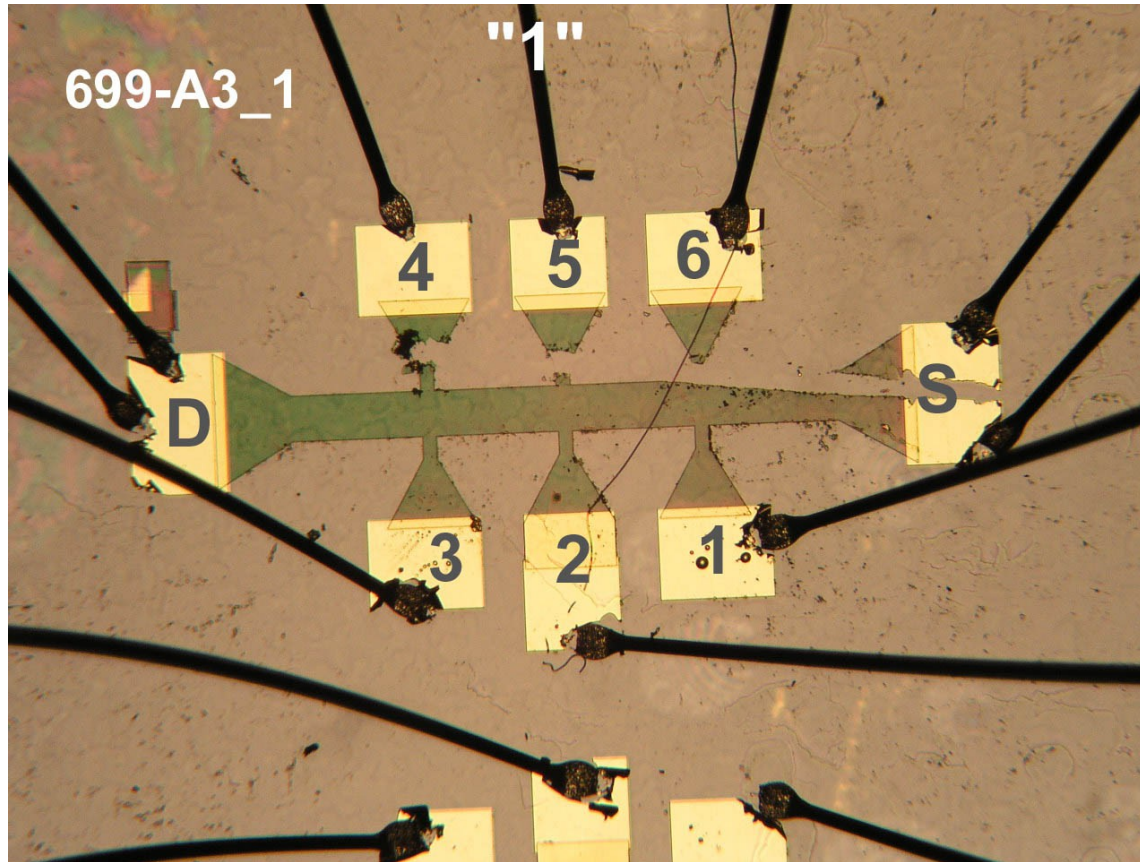
poruchy

Lithography-the layout of the device

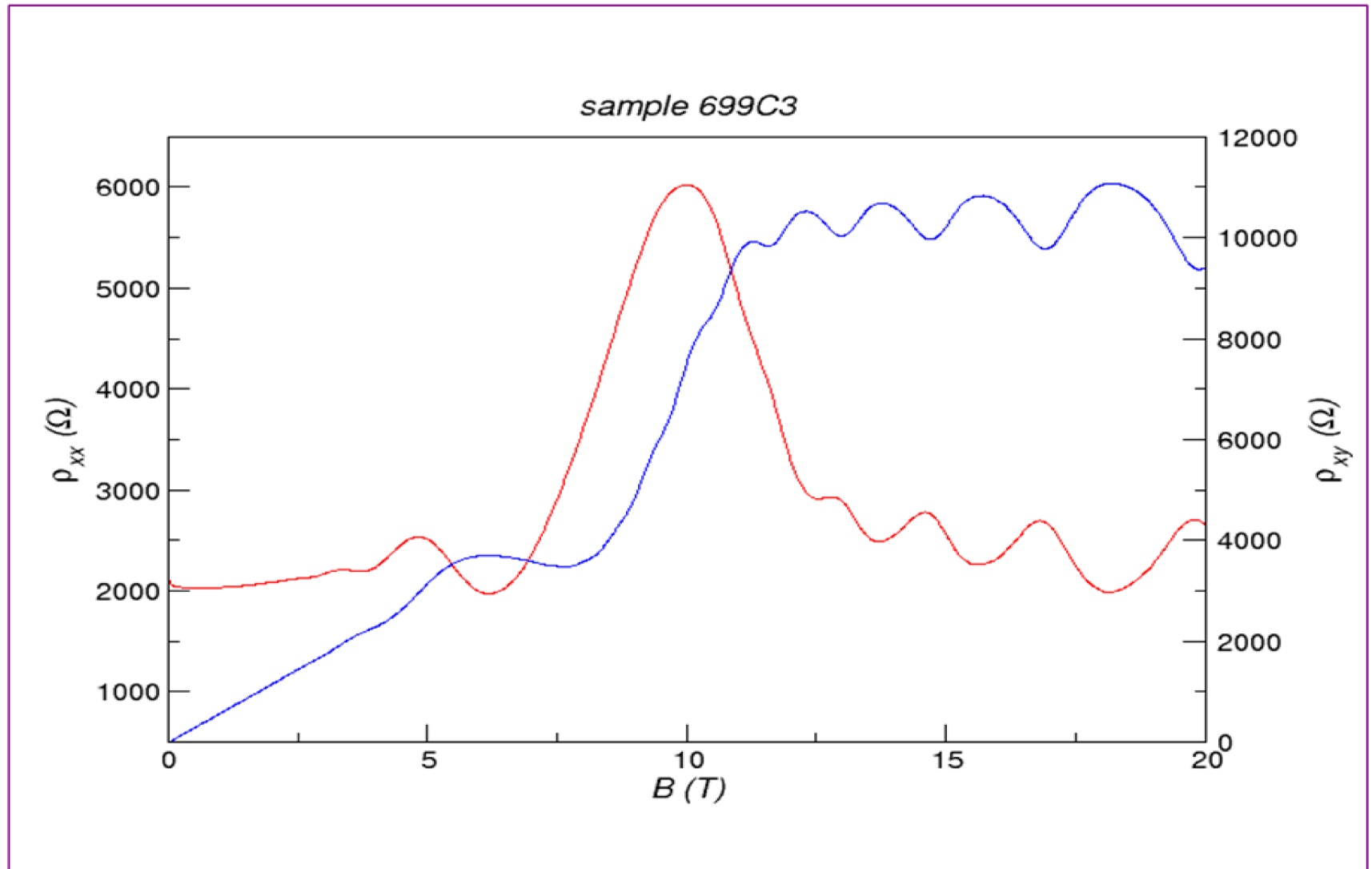


Grenoble december 2010

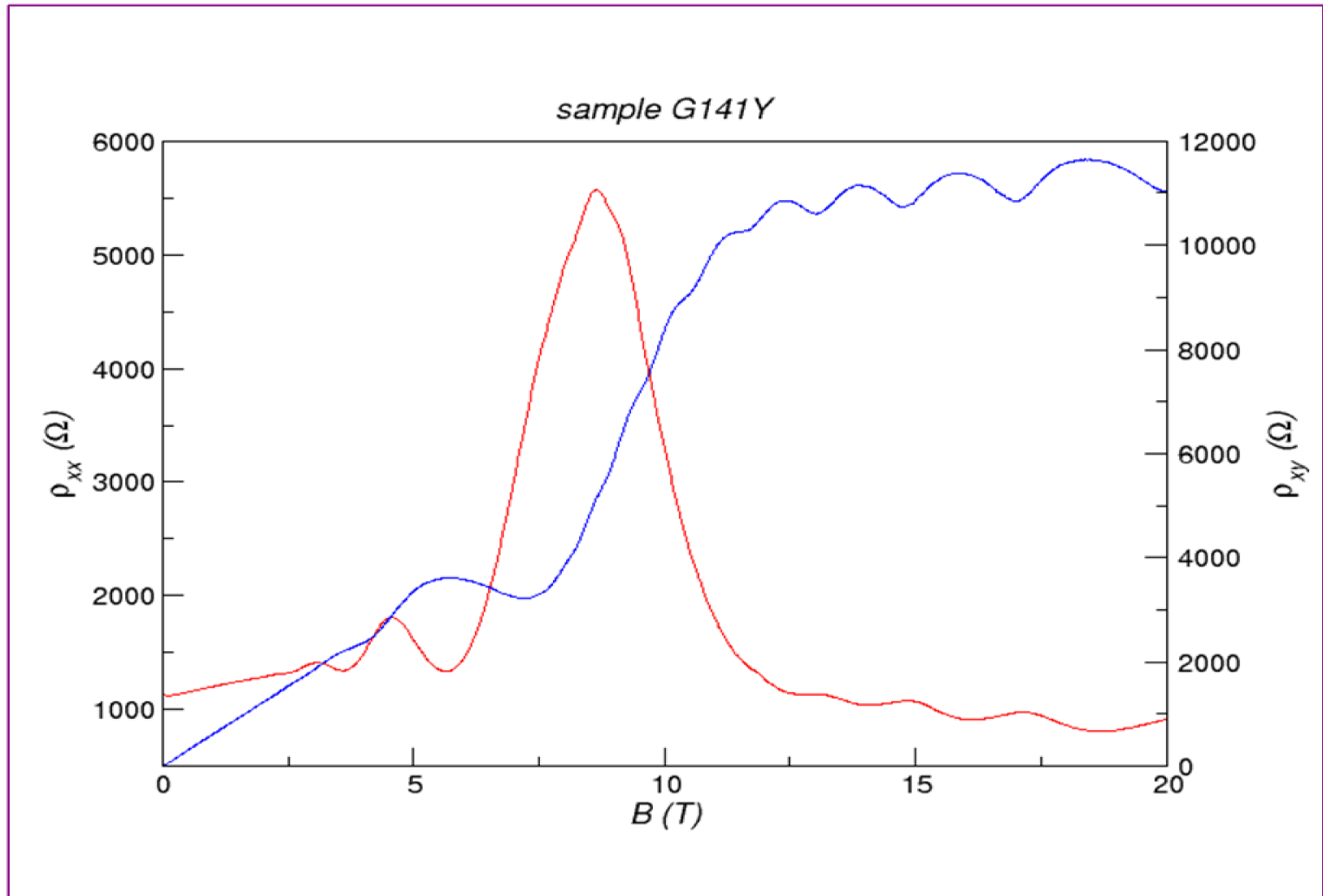
Real sample...



The sample 699: longitudinal and Hall magnetoresistances. Origin ITME Warsaw, Poland

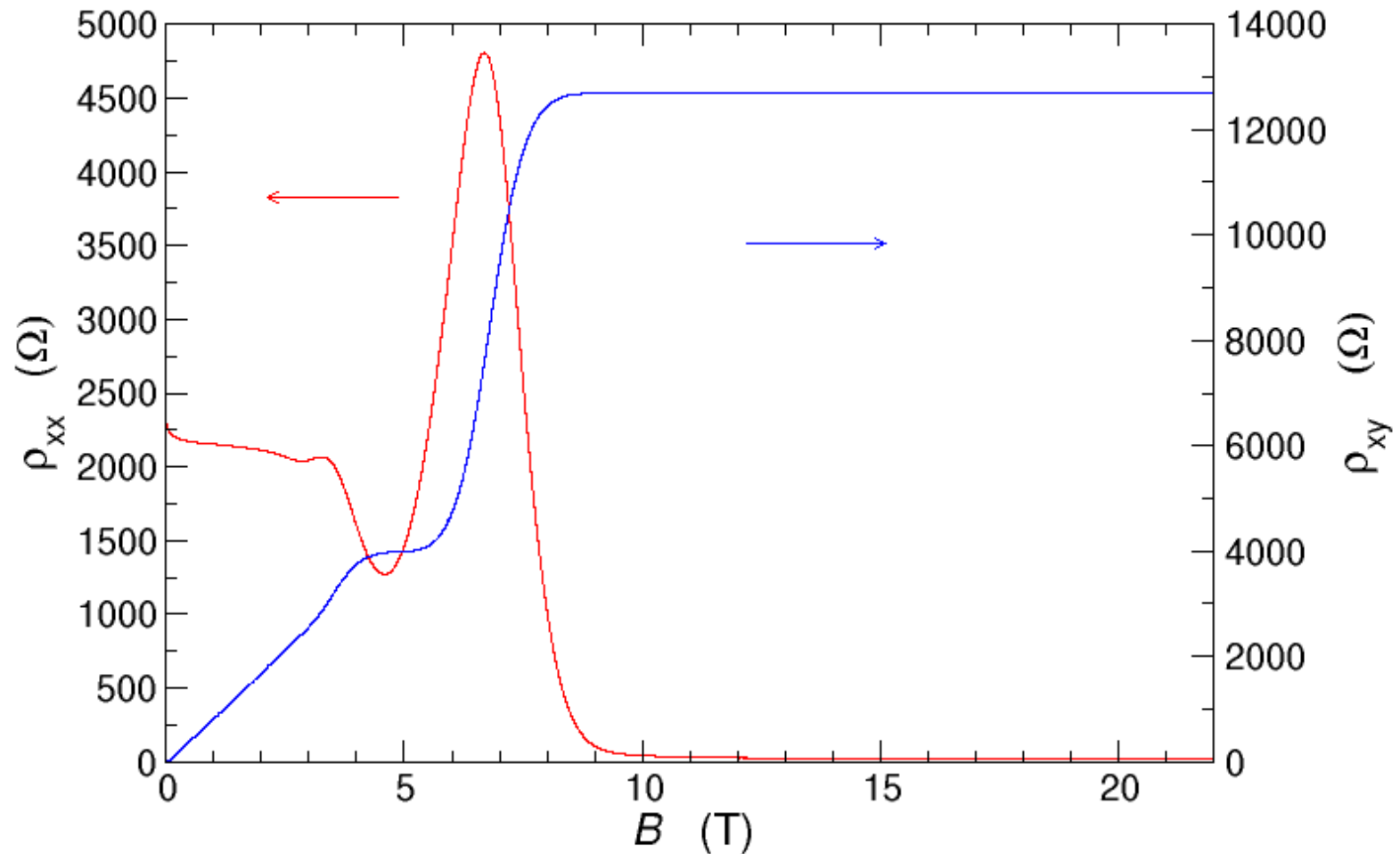


The sample 141: longitudinal and Hall magnetoresistances. Origin Linköping University.



Grenoble april 2012

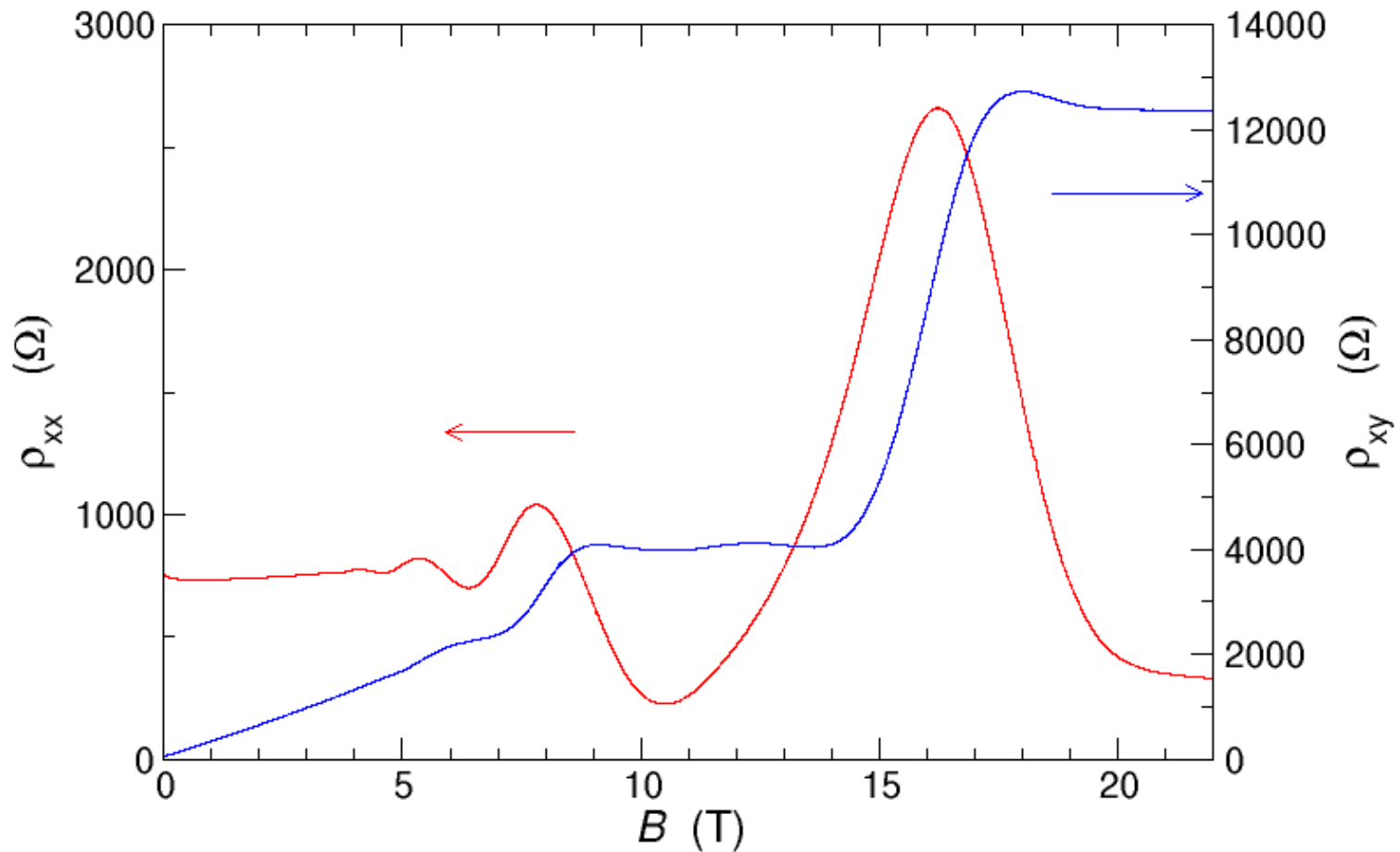
The sample 9052: longitudinal and Hall magnetoresistances. Origin ITME Warsaw, Poland



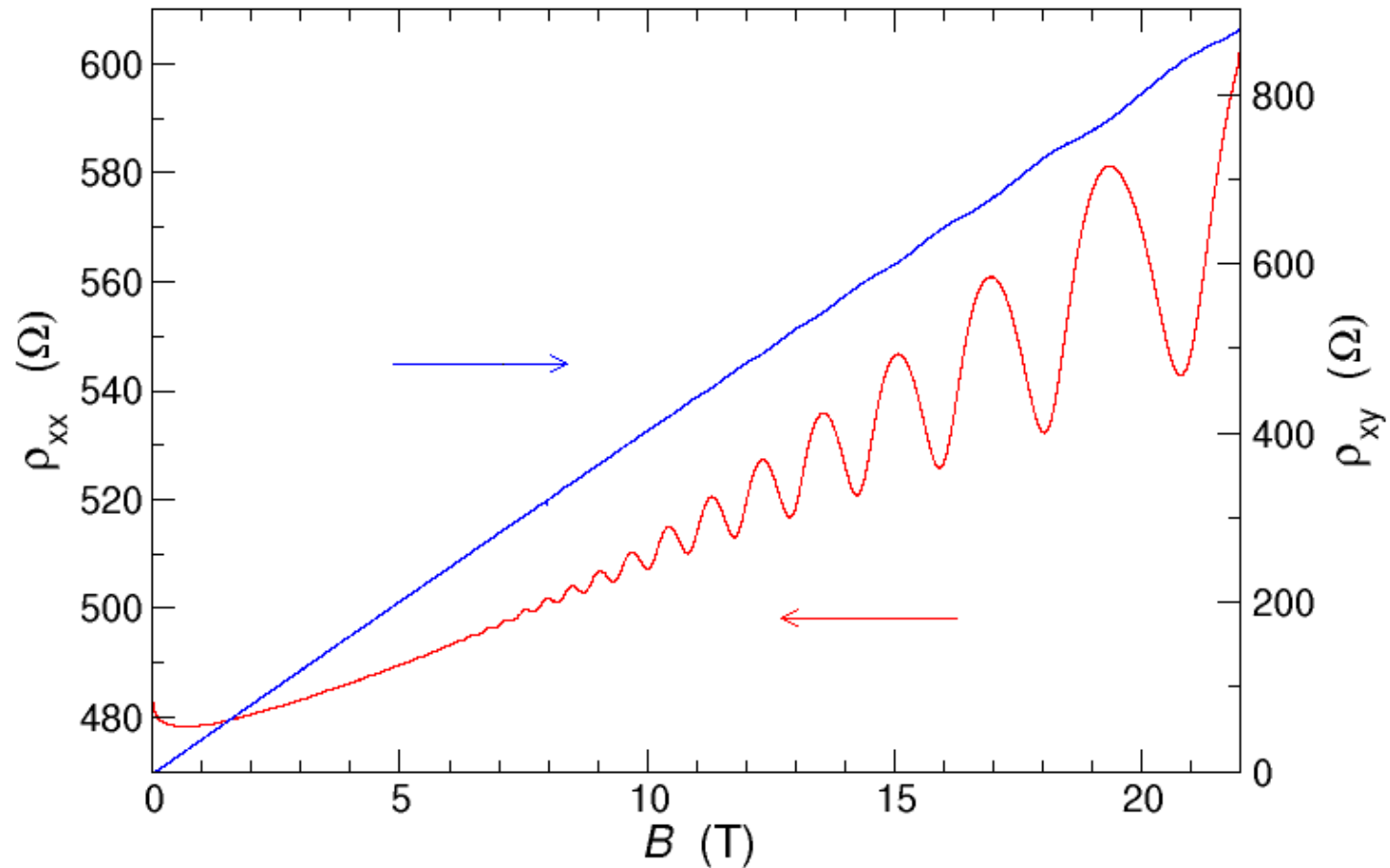
$$N_{\text{SdH}} = 9.69 \times 10^{11} \text{cm}^{-2}, N_{\text{H}} = 7.24 \times 10^{11} \text{cm}^{-2}, \mu_{\text{H}} = 3.89 \times 10^3 \text{cm}^2/\text{V}\cdot\text{sec}.$$

Influence of samples hydrogenation

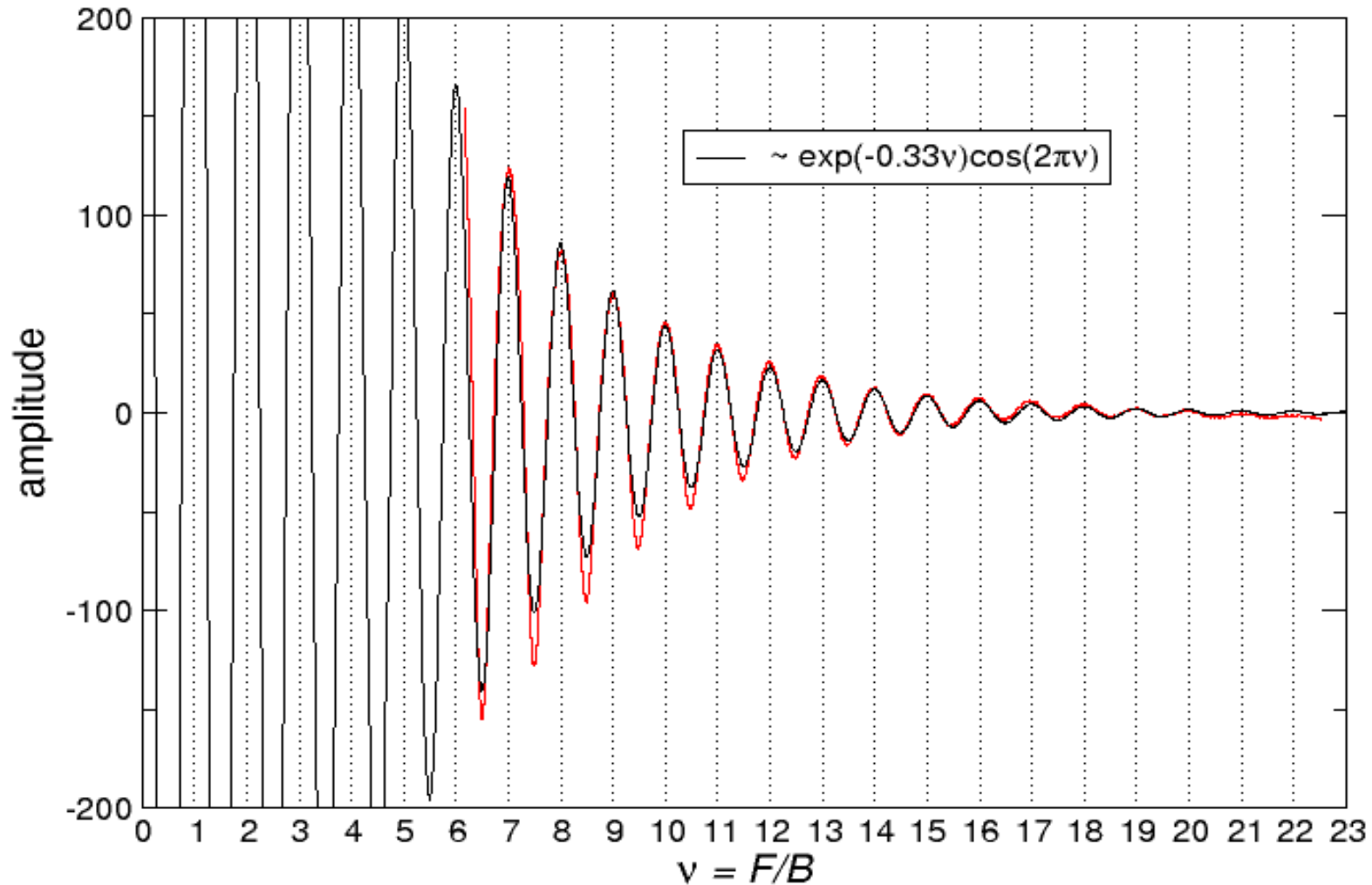
The sample 575: longitudinal and Hall magnetoresistances. Origin Linköping University, Sweden.



The sample 576: longitudinal and Hall magnetoresistances. Origin Linköping University, Sweden.

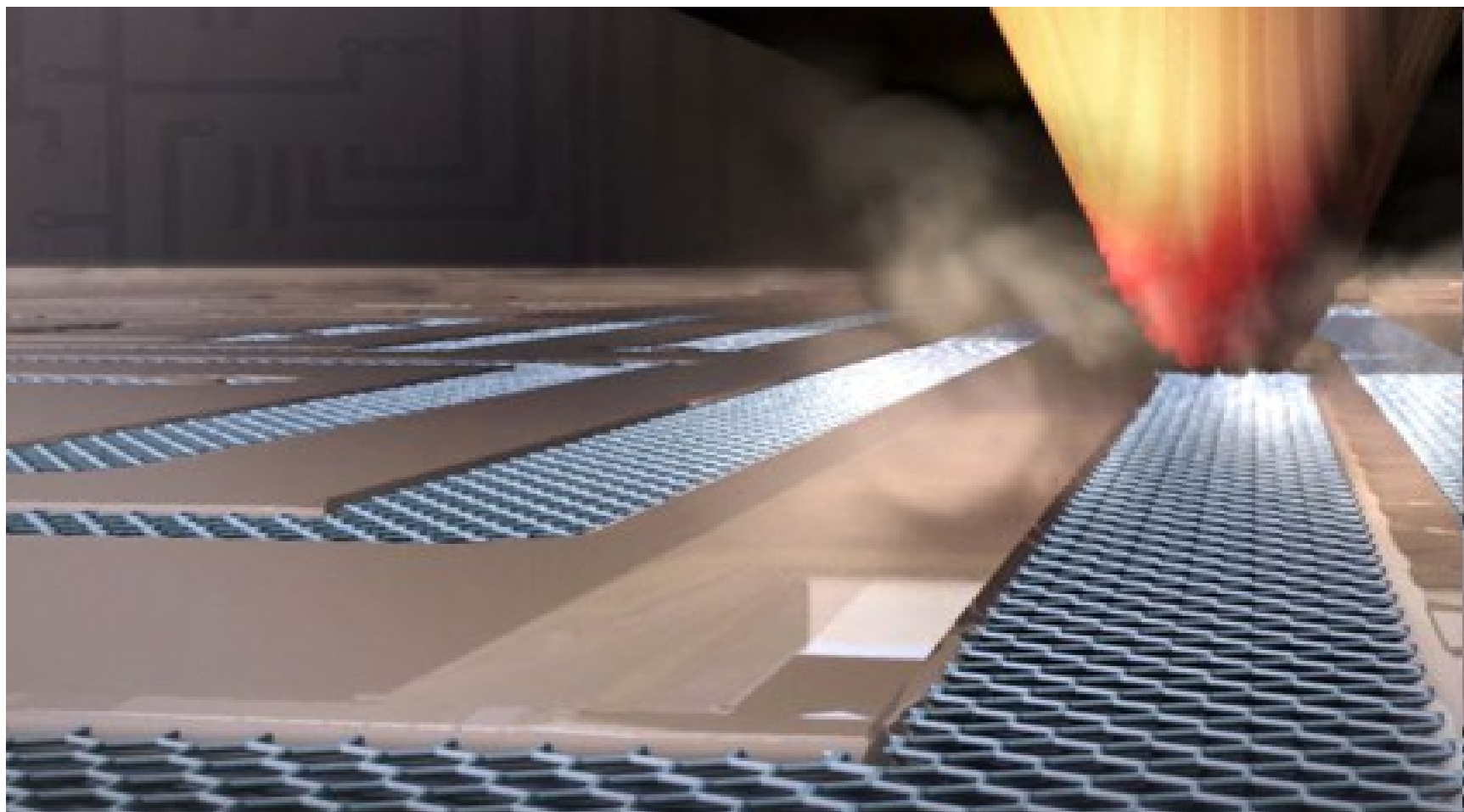


The sample 576: the oscillatory part of ρ_{xx} is compared with the oscillatory part of DOS of Dirac fermions.



Praktické aplikace

Grafenová mikroelektronika



Možné aplikace grafenu

- hodinky / kalendáře
- ohebný světelný panel
- elektronický papír
- mobilní telefony
- elektronické platby
- dotykové displeje,
- mikroelektronika
- kompozitní materiály
- přenosné počítače
- **elektrody fotovoltaiických článků**

Pramen: **denní tisk**

KONEC